



OptiMOS™ and StrongIRFET™ MOSFETs

Selection guide 2019

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OptiMOS™ and StrongIRFET™

20-300 V MOSFETs N-channel power MOSFETs

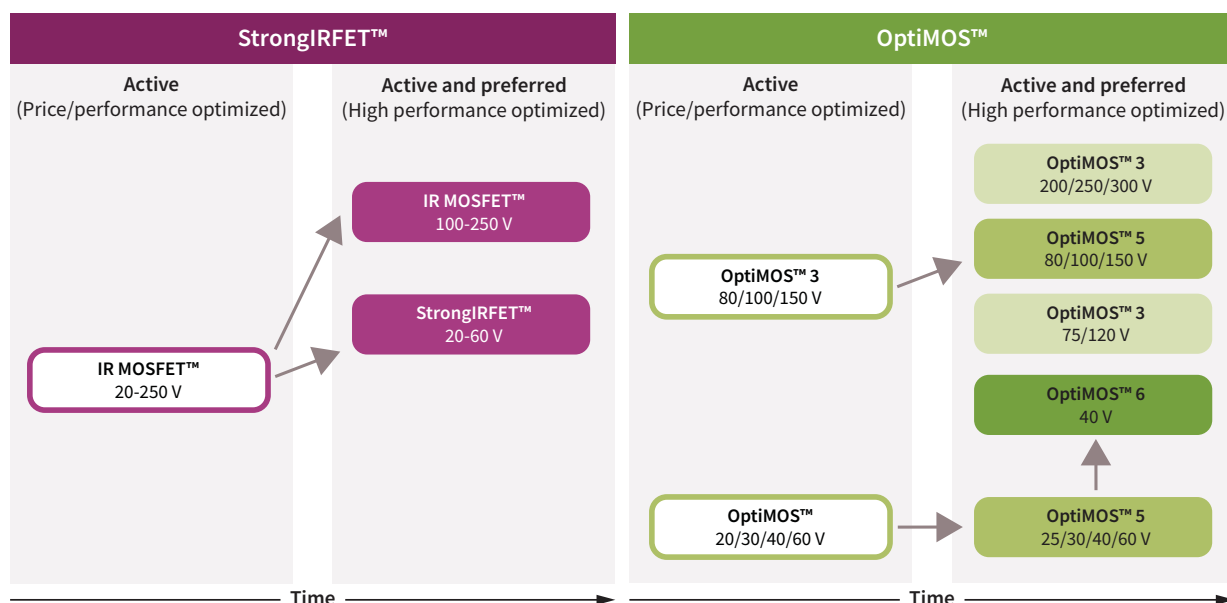
Infiniteon's semiconductors are designed to bring greater efficiency, power density and cost-effectiveness. The full range of OptiMOS™ and StrongIRFET™ power MOSFETs enables innovation and performance in applications such as switch mode power supplies (SMPS), battery powered applications, motor control and drives, inverters, and computing.

Infiniteon's highly innovative OptiMOS™ and StrongIRFET™ families consistently meet the highest quality and performance demands in key specifications for power system designs such as on-state resistance ($R_{DS(on)}$) and figure of merit (FOM).

OptiMOS™ power MOSFETs provide best-in-class performance. Features include ultralow $R_{DS(on)}$, as well as low charge for high switching frequency applications. StrongIRFET™ power MOSFETs are designed for drives applications and are ideal for designs with a low switching frequency, as well as those that require a high current carrying capability.

StrongIRFET™	OptiMOS™
Robust and excellent price/performance ratio	Best-in-class technology
Designed for industrial applications	Designed for high performance applications
Optimized for low switching frequency	Optimized for high switching frequency
High current carrying capability	Industry's best figure of merit
Rugged silicon	High efficiency and power density
	

Technology development and product family positioning

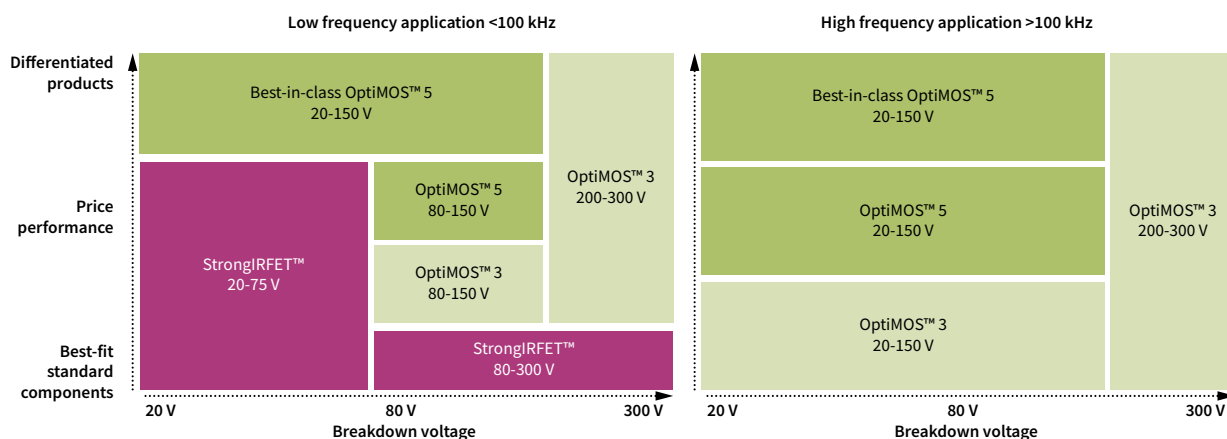


Infineon's power MOSFET 20-300 V product portfolio is divided into „active and preferred“, referring to the latest technology available offering best-in-class performance, as well as „active“, which consists of well-established technologies which complete this broad portfolio.

OptiMOS™ 6 power MOSFETs 40 V are the newest addition to the OptiMOS™ product family available either in SuperSO8 or PQFN 3.3 x 3.3 packages. This technology is the perfect solution when best-in-class (BiC) products and high efficiency over a wide range of output power are required. For the other voltage classes, from 25 V up to 150 V, OptiMOS™ 5 represents the latest generation in the market, offering either best-in-class (BiC) or price/performance solutions. For high frequency applications, the product portfolio is complemented by OptiMOS™ 3 power MOSFETs 40-50 V as standard components. The „active and preferred“ OptiMOS™ 3 power MOSFETs 75-120 V, as well as 200-300 V are the best fit portfolios either in low or high frequency applications with a range of products covering from BiC to standard parts.

StrongIRFET™ Gen. 1 is recommended for 20-300 V applications when BiC performance is not essential and cost is a more significant consideration.

The diagrams below summarize the recommended technology for best fit standard components, price/performance and differentiated products according to switching frequency.



Guidance for applications and voltage classes

OptiMOS™ and StrongIRFET™ portfolio, covering 20 up to 300 V MOSFETs, can address a broad range of needs from low to high switching frequencies. The tables below provide a guidance overview for the recommended OptiMOS™ or StrongIRFET™ products for each major sub-application and voltage class.

Recommended voltage			20-30 V	40 V	60 V	75-80 V	100 V	135-150 V	200 V	250 V	300 V
Battery powered	Low power Power tools, Multicopter, Battery, Industrial Drives	OptiMOS™	✓	✓	✓	✓					
		StrongIRFET™	✓	✓	✓	✓					
	High power (LEV, LSEV)	OptiMOS™			✓	✓	✓	✓	✓		
		StrongIRFET™			✓	✓	✓	✓	✓		
Inverters	Solar	OptiMOS™			✓	✓	✓	✓			
		StrongIRFET™			✓	✓	✓				
	UPS	slow switching									
		OptiMOS™	✓	✓	✓	✓	✓	✓	✓	✓	✓
		StrongIRFET™	✓	✓	✓	✓	✓	✓	✓	✓	✓
		fast switching									
		OptiMOS™	✓	✓	✓	✓	✓	✓	✓	✓	✓
		StrongIRFET™	✓	✓	✓	✓	✓	✓	✓	✓	✓
	Offline	OptiMOS™		✓	✓						
		StrongIRFET™		✓	✓						
SMPS	Adapter / Charger	OptiMOS™		✓	✓	✓	✓				
		StrongIRFET™		✓	✓	✓	✓				
	PC Power	OptiMOS™		✓	✓						
		StrongIRFET™		✓	✓						
	LCD TV	OptiMOS™			✓	✓	✓				
		StrongIRFET™			✓	✓	✓				
	Server	OptiMOS™		✓	✓	✓					
		StrongIRFET™		✓	✓	✓					
	AC-DC	OptiMOS™				✓	✓	✓	✓		
		StrongIRFET™				✓	✓				
	Telecom	OptiMOS™	✓	✓	✓	✓	✓	✓			
		StrongIRFET™	✓	✓	✓	✓	✓				

StrongIRFET™ recommended

OptiMOS™ recommended

StrongIRFET™ available

OptiMOS™ available

Space-saving and high performance packages

	TO-247	TO-220	D ² PAK	D ² PAK 7-pin	TO-Leadless
					
	Optimized for high power applications and high current capability				
Height [mm]	5.0	4.4	4.4	4.4	2.3
Outline [mm]	40.15 x 15.9	29.5 x 10.0	15.0 x 10.0	15.0 x 10.0	11.68 x 9.9
Current capability [A]	195.0	195.0	195.0	240.0	300.0
Thermal resistance R_{thJC} [K/W]	2.0	0.5	0.5	0.5	0.4

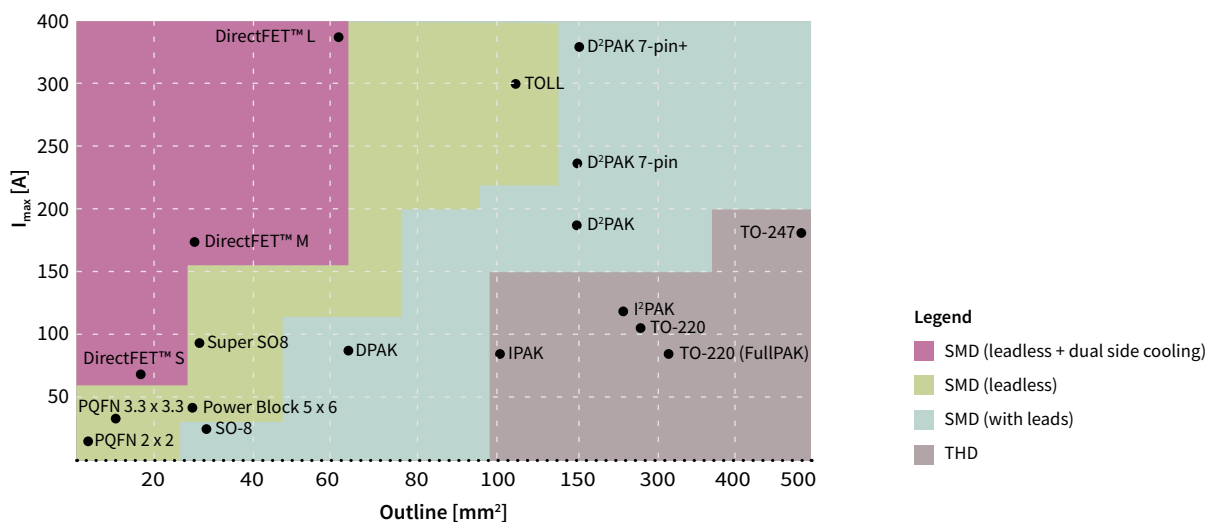
	SuperSO8	Power Block	PQFN 3.3 x 3.3	PQFN 2 x 2	DirectFET™
					
	For highest efficiency and power management	Significant design shrink	For highest efficiency and power management	Enables significant space saving	Best thermal behavior in a tiny footprint
Height [mm]	1.0	1.0	1.0	0.9	Small: 0.65 Medium: 0.65 Large: 0.71
Outline [mm]	5.15 x 6.15	5.0 x 6.0	3.3 x 3.3	2.0 x 2.0	Small: 4.8 x 3.8 Medium: 6.3 x 4.9 Large: 9.1 x 6.98
Current capability [A]	100.0	50.0	40.0	18.5	Small: 75.0 Medium: 180.0 Large: 375.0
Thermal resistance R_{thJC} [K/W]	0.8	1.5	3.2	11.1	0.5

Discrete and integrated packages

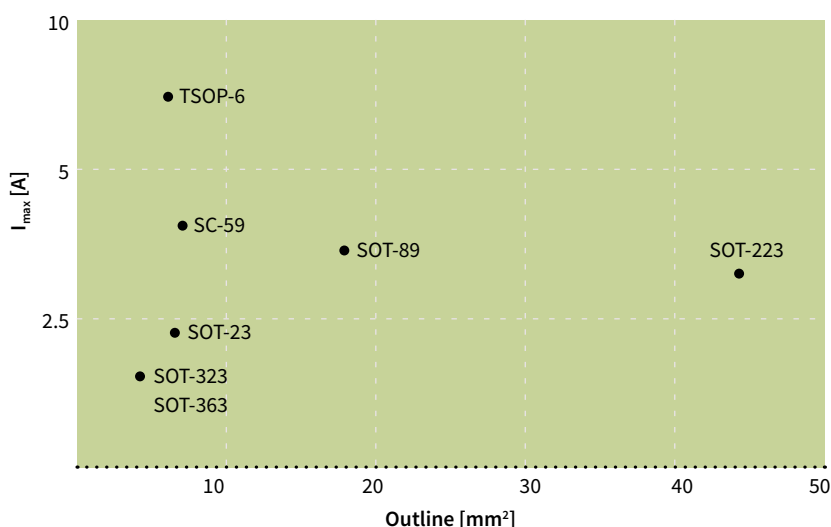
OptiMOS™ and StrongIRFET™ technologies are available in different packages to address the demands for higher current carrying capability and significant space saving.

The broad portfolio enables footprint reduction, boosted current rating, and optimized thermal performance. While the surface mount leadless devices enable footprint reduction, through-hole packages are characterized by a high power rating.

Furthermore, Infineon offers innovative packages such as DirectFET™ and TO-Leadless. DirectFET™ is designed for high frequency applications by offering the lowest parasitic resistance. This package is available in three different sizes: small, medium and large. TO-Leadless is optimized to handle currents of up to 300 A, increasing power density with a substantial reduction in footprint.



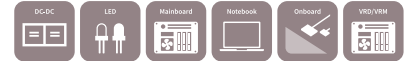
Small signal and small power MOSFETs



Small signal and small power MOSFETs are available in eight industry-standard package types ranging from the largest SOT-223 to the smallest SOT-363.

Products are offered in single, dual and complementary configurations and are suitable for a wide range of applications, including battery protection, LED lighting, low voltage drives and DC-DC converters.

OptiMOS™ and StrongIRFET™ 20 V (super) logic level



$R_{DS(on)}$ max @ $V_{GS}=10$ V [mΩ]	TO-252 (DPAK)	DirectFET™	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	SO-8	SOT-23
< 1		IRL6283MTRPBF $R_{DS(on)}=0.65$ mΩ			IRFH6200TRPBF $R_{DS(on)}=0.99$ mΩ		
2-4	IRLR6225TRPBF $R_{DS(on)}=4.0$ mΩ	IRL6297SDTRPBF** $R_{DS(on)}=3.8$ mΩ; dual			BSC026N02KS G $R_{DS(on)}=2.6$ mΩ IRLH6224TRPBF $R_{DS(on)}=3.0$ mΩ	IRF6201TRPBF $R_{DS(on)}=2.45$ mΩ	
4-10					BSC046N02KS G $R_{DS(on)}=4.6$ mΩ	IRF3717 $R_{DS(on)}=4.4$ mΩ	
> 10			IRLHS6242TRPBF $R_{DS(on)}=11.7$ mΩ IRLHS6276TRPBF** $R_{DS(on)}=45.0$ mΩ; dual				IRLML6244 ¹⁾ *** $R_{DS(on)}=21$ mΩ IRLML6246 ¹⁾ *** $R_{DS(on)}=46$ mΩ

OptiMOS™ and StrongIRFET™ 25 V logic level



$R_{DS(on)}$ max @ $V_{GS}=10$ V [mΩ]	DirectFET™	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	SO-8	SOT-23
< 1	IRF6718L2TRPBF $R_{DS(on)}=0.7$ mΩ BSB008NE2LX $R_{DS(on)}=0.8$ mΩ		BSZ009NE2LS5 ²⁾ $R_{DS(on)}=0.9$ mΩ	BSC009NE2LS $R_{DS(on)}=0.9$ mΩ BSC009NE2LS5 $R_{DS(on)}=0.9$ mΩ BSC009NE2LS5I** $R_{DS(on)}=0.95$ mΩ		
1-2	IRF6898MTRPBF** $R_{DS(on)}=1.1$ mΩ BSB012NE2LXI** $R_{DS(on)}=1.2$ mΩ IRF6717MTRPBF $R_{DS(on)}=1.25$ mΩ IRF6894MTRPBF** $R_{DS(on)}=1.3$ mΩ BSB013NE2LXI** $R_{DS(on)}=1.3$ mΩ IRF6797MTRPBF** $R_{DS(on)}=1.4$ mΩ IRF6716M $R_{DS(on)}=1.6$ mΩ IRF6715MTRPBF $R_{DS(on)}=1.6$ mΩ IRF6893MTRPBF** $R_{DS(on)}=1.6$ mΩ IRF6892STRPBF** $R_{DS(on)}=1.7$ mΩ IRF6795MTRPBF** $R_{DS(on)}=1.8$ mΩ		BSZ010NE2LS5 ²⁾ $R_{DS(on)}=1.0$ mΩ BSZ011NE2LS5 ²⁾ $R_{DS(on)}=1.1$ mΩ BSZ013NE2LS5I** $R_{DS(on)}=1.3$ mΩ BSZ014NE2LS5IF *** $R_{DS(on)}=1.45$ mΩ BSZ017NE2LS5I** $R_{DS(on)}=1.7$ mΩ BSZ018NE2LS $R_{DS(on)}=1.8$ mΩ BSZ018NE2LSI** $R_{DS(on)}=1.8$ mΩ	BSC010NE2LS $R_{DS(on)}=1.0$ mΩ BSC010NE2LSI** $R_{DS(on)}=1.05$ mΩ BSC014NE2LSI** $R_{DS(on)}=1.4$ mΩ IRFH5250D $R_{DS(on)}=1.4$ mΩ BSC015NE2LS5I** $R_{DS(on)}=1.5$ mΩ BSC018NE2LS $R_{DS(on)}=1.8$ mΩ BSC018NE2LSI** $R_{DS(on)}=1.8$ mΩ		
2-4	IRF6714MTRPBF $R_{DS(on)}=2.1$ mΩ BSF030NE2LQ $R_{DS(on)}=3.0$ mΩ BSF035NE2LQ $R_{DS(on)}=3.5$ mΩ IRF6811STRPBF** $R_{DS(on)}=3.7$ mΩ		BSZ031NE2LS5 $R_{DS(on)}=3.1$ mΩ BSZ033NE2LS5 $R_{DS(on)}=3.3$ mΩ BSZ036NE2LS $R_{DS(on)}=3.6$ mΩ BSZ037NE2LS5 ²⁾ $R_{DS(on)}=3.7$ mΩ BSZ039NE2LS5 ²⁾ $R_{DS(on)}=3.9$ mΩ	BSC024NE2LS $R_{DS(on)}=2.4$ mΩ BSC026NE2LS5 $R_{DS(on)}=2.6$ mΩ BSC032NE2LS $R_{DS(on)}=3.2$ mΩ	IRF8252 $R_{DS(on)}=2.7$ mΩ	
4-10	IRF6802SD $R_{DS(on)}=4.2$ mΩ IRF6710S2TRPBF $R_{DS(on)}=4.5$ mΩ IRF6712STRPBF $R_{DS(on)}=4.9$ mΩ IRF6810STRPBF** $R_{DS(on)}=5.2$ mΩ		IRFHM8228TRPBF $R_{DS(on)}=5.2$ mΩ BSZ060NE2LS $R_{DS(on)}=6.0$ mΩ IRFHM8235TRPBF $R_{DS(on)}=7.7$ mΩ	BSC050NE2LS $R_{DS(on)}=5.0$ mΩ		
> 10		IRFHS8242 $R_{DS(on)}=13$ mΩ				IRFML8244 $R_{DS(on)}=24$ mΩ

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* Optimized for resonant applications (e.g. LLC converter)

** Monolithically integrated Schottky-like diode

*** $R_{DS(on)}$ max @ $V_{GS}=4.5$ V

¹⁾ 2.5 V_{GS} capable

²⁾ Coming soon



OptiMOS™ and StrongIRFET™ 25 V/30 V in Power Stage 3 x 3 and 5 x 6



Part number	Package	Monolithically integrated Schottky like diode	BV _{DSS} [V]	R _{DS(on), max.} [mΩ] @ V _{GS} =4.5 V max.		Q _g [nC] @ V _{GS} =4.5 V typ.	
				High-side	Low-side	High-side	Low-side
BSZ0910ND	TISON 3 x 3	–	30	13	13	4.0	4.0
BSZ0909ND	TISON 3 x 3	–	30	25	25	1.8	1.8
BSC0910NDI	TISON 5 x 6	✓	25	5.9	1.6	7.7	25.0
BSC0911ND	TISON 5 x 6	–	25	4.8	1.7	7.7	25.0
BSC0921NDI	TISON 5 x 6	✓	30	7.0	2.1	5.8	21.0
BSC0923NDI	TISON 5 x 6	✓	30	7.0	3.7	5.2	12.2
BSC0924NDI	TISON 5 x 6	✓	30	7.0	5.2	5.2	8.6
BSC0925ND	TISON 5 x 6	–	30	6.4	6.4	5.2	6.7

OptiMOS™ and StrongIRFET™ 25 V/30 V in Power Block 5 x 6 and 5 x 4



Part number	Package	Monolithically integrated Schottky like diode	BV _{DSS} [V]	R _{DS(on), max.} [mΩ] @ V _{GS} =4.5 V max.		Q _g [nC] @ V _{GS} =4.5 V typ.	
				High-side	Low-side	High-side	Low-side
BSG0810NDI	TISON 5 x 6	✓	25	4.0	1.2	5.6	16.0
BSG0811ND	TISON 5 x 6	–	25	4.0	1.1	5.6	20.0
BSG0813NDI	TISON 5 x 6	✓	25	4.0	1.7	5.6	12.0
IRFH4257DTRPBF	PQFN 5 x 4	✓	25	4.7	1.8	9.7	23.0

OptiMOS™ and StrongIRFET™ 30 V logic level



$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-220
<1			IPB009N03L G $R_{DS(on)}=0.95\text{ mΩ}$	
1-2		IRLS3813TRL PBF $R_{DS(on)}=1.95\text{ mΩ}$		IRLB3813PBF $R_{DS(on)}=1.95\text{ mΩ}$
2-4	IRLR8743TRPBF $R_{DS(on)}=3.1\text{ mΩ}$			IRLB8314PBF $R_{DS(on)}=2.4\text{ mΩ}$
	IPD031N03L G $R_{DS(on)}=3.1\text{ mΩ}$			IRL3713PBF $R_{DS(on)}=3.0\text{ mΩ}$
		IPB034N03L G $R_{DS(on)}=3.4\text{ mΩ}$		IRLB8743PBF $R_{DS(on)}=3.2\text{ mΩ}$
	IPD040N03L G $R_{DS(on)}=4.0\text{ mΩ}$			IPP034N03L G $R_{DS(on)}=3.4\text{ mΩ}$
4-10	IPD050N03L G $R_{DS(on)}=5.0\text{ mΩ}$	IPB042N03L G $R_{DS(on)}=4.2\text{ mΩ}$		IPP042N03L G $R_{DS(on)}=4.2\text{ mΩ}$
	IRLR8726TRPBF $R_{DS(on)}=5.8\text{ mΩ}$	IPB055N03L G $R_{DS(on)}=5.5\text{ mΩ}$		IRLB8748PBF $R_{DS(on)}=4.8\text{ mΩ}$
	IPD060N03L G $R_{DS(on)}=6.0\text{ mΩ}$	IPB065N03L G $R_{DS(on)}=6.5\text{ mΩ}$		IPP055N03L G $R_{DS(on)}=5.5\text{ mΩ}$
	IPD075N03L G $R_{DS(on)}=7.5\text{ mΩ}$	IPB080N03L G $R_{DS(on)}=8.0\text{ mΩ}$		IRL8113PBF $R_{DS(on)}=6.0\text{ mΩ}$
	IRLR8729TRPBF $R_{DS(on)}=8.9\text{ mΩ}$			IRLB8721PBF $R_{DS(on)}=8.7\text{ mΩ}$
	IPD090N03L G $R_{DS(on)}=9.0\text{ mΩ}$			
	IPD135N03L G $R_{DS(on)}=13.5\text{ mΩ}$			
	IRLR3103 $R_{DS(on)}=19.0\text{ mΩ}$			

OptiMOS™ and StrongIRFET™ 30 V logic level



$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	Bare die ($R_{DS(on)}$ typ.)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	TO-Leadless
<1					IPT004N03L $R_{DS(on)}=0.4\text{ mΩ}$
1-2				IRFH8303TRPBF $R_{DS(on)}=1.1\text{ mΩ}$	
				BSC011N03LS $R_{DS(on)}=1.1\text{ mΩ}$	
				BSC011N03LSI** $R_{DS(on)}=1.1\text{ mΩ}$	
				BSC011N03LST $R_{DS(on)}=1.1\text{ mΩ}$	
				IRFH8307TRPBF $R_{DS(on)}=1.3\text{ mΩ}$	
		IRF8301MTRPBF $R_{DS(on)}=1.5\text{ mΩ}$		BSC0500NSI** $R_{DS(on)}=1.3\text{ mΩ}$	
			BSZ0500NSI** $R_{DS(on)}=1.5\text{ mΩ}$	BSC014N03LS G $R_{DS(on)}=1.4\text{ mΩ}$	
		IRF8302MTRPBF** $R_{DS(on)}=1.8\text{ mΩ}$	BSZ019N03LS $R_{DS(on)}=1.9\text{ mΩ}$	BSC0901NS $R_{DS(on)}=1.9\text{ mΩ}$	
			BSZ0901NS $R_{DS(on)}=2.0\text{ mΩ}$	BSC0501NSI** $R_{DS(on)}=1.9\text{ mΩ}$	
	IPC055N03L3*** $R_{DS(on)}=2.7\text{ mΩ}$		BSZ0501NSI** $R_{DS(on)}=2.0\text{ mΩ}$	BSC0901NSI** $R_{DS(on)}=2.0\text{ mΩ}$	

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** Monolithically integrated Schottky-like diode

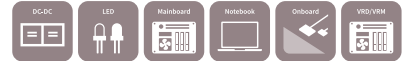
*** $R_{DS(on)}$ typ. @ $V_{GS}=4.5\text{ V}$

OptiMOS™ and StrongIRFET™ 30 V logic level



$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	Bare die ($R_{DS(on) typ.}$)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	SO-8	SO-8 Dual	PQFN 2 x 2
2-4		IRF8304MTRPBF $R_{DS(on)}=2.2\text{ mΩ}$	BSZ0901NSI** $R_{DS(on)}=2.1\text{ mΩ}$	BSC020N03LS G $R_{DS(on)}=2.0\text{ mΩ}$			
	IPC042N03L3**** $R_{DS(on)}=3.7\text{ mΩ}$		IRLHM620TRPBF $R_{DS(on)}=2.5\text{ mΩ}$	BSC0502NSI** $R_{DS(on)}=2.4\text{ mΩ}$			
		IRF8306MTRPBF** $R_{DS(on)}=2.5\text{ mΩ}$	BSZ0902NS $R_{DS(on)}=2.6\text{ mΩ}$	BSC025N03LS G $R_{DS(on)}=2.5\text{ mΩ}$			
				BSC0902NS $R_{DS(on)}=2.6\text{ mΩ}$			
				IRF8252TRPBF $R_{DS(on)}=2.7\text{ mΩ}$			
			BSZ0902NSI** $R_{DS(on)}=2.8\text{ mΩ}$	BSC0902NSI** $R_{DS(on)}=2.8\text{ mΩ}$	IRF8788TRPBF $R_{DS(on)}=2.8\text{ mΩ}$		
			BSZ0502NSI** $R_{DS(on)}=2.8\text{ mΩ}$	IRFH8316TRPBF $R_{DS(on)}=2.95\text{ mΩ}$			
				BSC030N03LS G $R_{DS(on)}=3.0\text{ mΩ}$			
			BSZ0503NSI** $R_{DS(on)}=3.4\text{ mΩ}$	IRFH8318TRPBF $R_{DS(on)}=3.1\text{ mΩ}$			
			IRLHM630*** $R_{DS(on)}=3.5\text{ mΩ}$	BSC0503NSI** $R_{DS(on)}=3.2\text{ mΩ}$	IRF7862TRPBF $R_{DS(on)}=3.3\text{ mΩ}$		
			BSZ035N03LS G $R_{DS(on)}=3.5\text{ mΩ}$	BSC034N03LS G $R_{DS(on)}=3.4\text{ mΩ}$	IRF8734TRPBF $R_{DS(on)}=3.5\text{ mΩ}$		
			IRFHM830 $R_{DS(on)}=3.8\text{ mΩ}$	BSC0504NSI** $R_{DS(on)}=3.7\text{ mΩ}$			
			BSZ0904NSI** $R_{DS(on)}=4.0\text{ mΩ}$	BSC0904NSI** $R_{DS(on)}=3.7\text{ mΩ}$			
			IRFHM830D $R_{DS(on)}=4.3\text{ mΩ}$	IRFH8324TRPBF $R_{DS(on)}=4.1\text{ mΩ}$			
4-10			BSZ0506NS $R_{DS(on)}=4.4\text{ mΩ}$	BSC042N03LS G $R_{DS(on)}=4.2\text{ mΩ}$			
			IRFHM8326TRPBF $R_{DS(on)}=4.7\text{ mΩ}$	BSC0906NS $R_{DS(on)}=4.5\text{ mΩ}$			
				IRFH8321TRPBF $R_{DS(on)}=4.9\text{ mΩ}$			
	IPC028N03L3 $R_{DS(on)}=5.0\text{ mΩ}$		BSZ050N03LS G $R_{DS(on)}=5.0\text{ mΩ}$	IRFH8325TRPBF $R_{DS(on)}=5.0\text{ mΩ}$	IRF8736TRPBF $R_{DS(on)}=4.8\text{ mΩ}$		
			BSZ058N03LS G $R_{DS(on)}=5.8\text{ mΩ}$	BSC050N03LS G $R_{DS(on)}=5.0\text{ mΩ}$			
	IPC022N03L3 $R_{DS(on)}=5.3\text{ mΩ}$		IRFHM8329TRPBF $R_{DS(on)}=6.1\text{ mΩ}$	BSC052N03LS $R_{DS(on)}=5.2\text{ mΩ}$			
			BSZ065N03LS $R_{DS(on)}=6.5\text{ mΩ}$	BSC057N03LS G $R_{DS(on)}=5.7\text{ mΩ}$			
		IRF8327S2 $R_{DS(on)}=7.3\text{ mΩ}$	IRFHM8330TRPBF $R_{DS(on)}=6.6\text{ mΩ}$	IRFH8330TRPBF $R_{DS(on)}=6.6\text{ mΩ}$			
			BSZ0994NS $R_{DS(on)}=7.0\text{ mΩ}$	BSC080N03LS G $R_{DS(on)}=8.0\text{ mΩ}$			
			IRFHM831 $R_{DS(on)}=7.8\text{ mΩ}$	IRFH8334TRPBF $R_{DS(on)}=9.0\text{ mΩ}$	IRF8721TRPBF $R_{DS(on)}=8.5\text{ mΩ}$		
			BSZ088N03LS G $R_{DS(on)}=8.8\text{ mΩ}$	BSC090N03LS G $R_{DS(on)}=9.0\text{ mΩ}$	IRF8714TRPBF $R_{DS(on)}=8.7\text{ mΩ}$		
			IRFHM8334TRPBF $R_{DS(on)}=9.0\text{ mΩ}$	BSC0909NS $R_{DS(on)}=9.2\text{ mΩ}$			
			BSZ100N03LS G $R_{DS(on)}=10.0\text{ mΩ}$				
	IPC014N03L3 $R_{DS(on)}=10.3\text{ mΩ}$		BSZ0909NS $R_{DS(on)}=12.0\text{ mΩ}$	BSC120N03LS G $R_{DS(on)}=12.0\text{ mΩ}$	IRF8707TRPBF $R_{DS(on)}=11.9\text{ mΩ}$	IRF7907TRPBF $R_{DS(on)}=11.8\text{ mΩ}+16.4\text{ mΩ}$	IRLHS6342*** $R_{DS(on)}=16\text{ mΩ}$
10-63			IRFHM8337TRPBF $R_{DS(on)}=12.4\text{ mΩ}$	IRFH8337TRPBF $R_{DS(on)}=12.8\text{ mΩ}$	IRL6342 ¹⁾ *** $R_{DS(on)}=14.6\text{ mΩ}$	IRF8513TRPBF $R_{DS(on)}=2.7\text{ mΩ}+15.5\text{ mΩ}$	IRFHS8342 $R_{DS(on)}=16\text{ mΩ}$
			BSZ130N03LS G $R_{DS(on)}=13.0\text{ mΩ}$		IRL6372 ¹⁾ *** $R_{DS(on)}=18\text{ mΩ; dual}$	IRF8313TRPBF $R_{DS(on)}=15.5\text{ mΩ}+15.5\text{ mΩ}$	IRLHS6376*** $R_{DS(on)}=63\text{ mΩ; dual}$
			IRFHM8363TRPBF $R_{DS(on)}=14.9\text{ mΩ}$			IRF7905TRPBF $R_{DS(on)}=17.1\text{ mΩ}+21.8\text{ mΩ}$	
				BSC072N03LD G $R_{DS(on)}=7.2\text{ mΩ}$			
2 x 7.2				BSC150N03LD G $R_{DS(on)}=15.0\text{ mΩ}$			
2 x 15							

OptiMOST™ and StrongIRFET™ 30 V logic level 5 V optimized



$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	PQFN 3.3 x 3.3	SuperSO8	SO-8	SO-8 Dual	SOT-23	TSOP-6
1-2		BSC014N03MS G $R_{DS(on)}=1.4\text{ mΩ}$				
		BSC016N03MS G $R_{DS(on)}=1.6\text{ mΩ}$				
		BSC020N03MS G $R_{DS(on)}=2.0\text{ mΩ}$				
2-4		BSC025N03MS G $R_{DS(on)}=2.5\text{ mΩ}$	BSO033N03MS G $R_{DS(on)}=3.3\text{ mΩ}$			
	BSZ035N03MS G $R_{DS(on)}=3.5\text{ mΩ}$	BSC030N03MS G $R_{DS(on)}=3.0\text{ mΩ}$	BSO040N03MS G $R_{DS(on)}=4.0\text{ mΩ}$			
		BSC042N03MS G $R_{DS(on)}=4.2\text{ mΩ}$				
4-10	BSZ050N03MS G $R_{DS(on)}=5.0\text{ mΩ}$	BSC050N03MS G $R_{DS(on)}=5.0\text{ mΩ}$				
		BSC057N03MS G $R_{DS(on)}=5.7\text{ mΩ}$				
	BSZ058N03MS G $R_{DS(on)}=5.8\text{ mΩ}$	BSC080N03MS G $R_{DS(on)}=8.0\text{ mΩ}$				
	BSZ088N03MS G $R_{DS(on)}=8.8\text{ mΩ}$	BSC090N03MS G $R_{DS(on)}=9.0\text{ mΩ}$				
	BSZ100N03MS G $R_{DS(on)}=10.0\text{ mΩ}$	BSC100N03MS G $R_{DS(on)}=10.0\text{ mΩ}$				
	BSZ130N03MS G $R_{DS(on)}=13.0\text{ mΩ}$	BSC120N03MS G $R_{DS(on)}=12.0\text{ mΩ}$	BSO110N03MS G $R_{DS(on)}=11.0\text{ mΩ}$			
>10					IRLML0030 $R_{DS(on)}=27\text{ mΩ}$	IRLTS6342*** $R_{DS(on)}=14.6\text{ mΩ}$
					IRLML6344 ¹⁾ *** $R_{DS(on)}=29\text{ mΩ}$	IRFTS8342 $R_{DS(on)}=19\text{ mΩ}$
					IRLML6346 ¹⁾ *** $R_{DS(on)}=63\text{ mΩ}$	
					IRLML2030 $R_{DS(on)}=100\text{ mΩ}$	
2 x 15				BSO150N03MD G $R_{DS(on)}=15.0\text{ mΩ}$		
2 x 22				BSO220N03MD G $R_{DS(on)}=22.0\text{ mΩ}$		



OptiMOST™ and StrongIRFET™ 40 V normal level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-220	TO-247	Bare die ($R_{DS(on)}$ typ.)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	TO-220 FullPAK
<1			IRFS7430TRL7PP $R_{DS(on)}=0.75\text{ mΩ}$			IPC218N04N3 $R_{DS(on)}=0.9\text{ mΩ}$				
1-2		IRFS7430TRLPBF $R_{DS(on)}=1.3\text{ mΩ}$	IRFS7434TRL7PP $R_{DS(on)}=1.0\text{ mΩ}$	IRFB7430PBF $R_{DS(on)}=1.3\text{ mΩ}$	IRFP7430PBF $R_{DS(on)}=1.3\text{ mΩ}$	IPC171N04N $R_{DS(on)}=1.1\text{ mΩ}$	IRF7739L1TRPBF $R_{DS(on)}=1.0\text{ mΩ}$		IRFH7084TRPBF $R_{DS(on)}=1.25\text{ mΩ}$	
		IPB015N04N G $R_{DS(on)}=1.5\text{ mΩ}$	IPB011N04N G $R_{DS(on)}=1.1\text{ mΩ}$	IPP015N04N G $R_{DS(on)}=1.5\text{ mΩ}$			IRF7480MTRPBF $R_{DS(on)}=1.2\text{ mΩ}$		IRFH7004TRPBF $R_{DS(on)}=1.4\text{ mΩ}$	
		IRFS3004 $R_{DS(on)}=1.75\text{ mΩ}$	IRFS3004-7P $R_{DS(on)}=1.25\text{ mΩ}$				IRF7946TRPBF $R_{DS(on)}=1.4\text{ mΩ}$		BSC017N04NS G $R_{DS(on)}=1.7\text{ mΩ}$	
		IRFS7434TRLPBF $R_{DS(on)}=1.6\text{ mΩ}$	IRFS7437TRL7PP $R_{DS(on)}=1.4\text{ mΩ}$	IRFB7434PBF $R_{DS(on)}=1.6\text{ mΩ}$			BSB015N04NX3 G $R_{DS(on)}=1.5\text{ mΩ}$		IRF40H210 $R_{DS(on)}=1.7\text{ mΩ}$	
		IRFS7437TRLPBF $R_{DS(on)}=1.8\text{ mΩ}$	IPB020N04N G $R_{DS(on)}=2.0\text{ mΩ}$	IRFB7437PBF $R_{DS(on)}=2.0\text{ mΩ}$			IRF40DM229 $R_{DS(on)}=1.85\text{ mΩ}$		BSC019N04NS G $R_{DS(on)}=1.9\text{ mΩ}$	
2-4	IRFR7440TRPBF $R_{DS(on)}=2.4\text{ mΩ}$			IPP023N04N G $R_{DS(on)}=2.3\text{ mΩ}$			IRF7483MTRPBF $R_{DS(on)}=2.3\text{ mΩ}$		IRFH7440TRPBF $R_{DS(on)}=2.4\text{ mΩ}$	
	IRFR7446TRPBF $R_{DS(on)}=3.9\text{ mΩ}$	IRFS7440TRLPBF $R_{DS(on)}=2.5\text{ mΩ}$		IRFB7440PBF $R_{DS(on)}=2.5\text{ mΩ}$					BSC030N04NS G $R_{DS(on)}=3.0\text{ mΩ}$	
		IRF1404S $R_{DS(on)}=4.0\text{ mΩ}$		IRFB7446PBF $R_{DS(on)}=3.3\text{ mΩ}$					IRFH7446TRPBF $R_{DS(on)}=3.3\text{ mΩ}$	
4-10				IPP041N04N G $R_{DS(on)}=4.1\text{ mΩ}$					BSC054N04NS G $R_{DS(on)}=5.4\text{ mΩ}$	IPA041N04N G $R_{DS(on)}=4.1\text{ mΩ}$
	IRF40R207 $R_{DS(on)}=5.1\text{ mΩ}$			IRF40B207 $R_{DS(on)}=4.5\text{ mΩ}$						
				IPP048N04N G $R_{DS(on)}=4.8\text{ mΩ}$						
>10								BSZ105N04NS G $R_{DS(on)}=10.5\text{ mΩ}$		
								BSZ165N04NS G $R_{DS(on)}=16.5\text{ mΩ}$		

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1) 2.5 V_{GS} capable

*** $R_{DS(on)}$ max @ $V_{GS}=4.5\text{ V}$



OptiMOS™ and StrongIRFET™ 40 V logic level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-220	TO-247	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	TO-Leadless
<1			IRL40SC228 $R_{DS(on)}=0.65\text{ mΩ}$			IRL7472L1TRPBF $R_{DS(on)}=0.45\text{ mΩ}$		BSC007N04LS6 $R_{DS(on)}=0.7\text{ mΩ}$	IRL40T209 $R_{DS(on)}=0.8\text{ mΩ}$
			IRL40SC209 $R_{DS(on)}=0.8\text{ mΩ}$						
1-2		IPB015N04L G $R_{DS(on)}=1.5\text{ mΩ}$	IPB011N04L G $R_{DS(on)}=1.1\text{ mΩ}$	IRL40B209 $R_{DS(on)}=1.25\text{ mΩ}$	IRLP3034PBF $R_{DS(on)}=1.7\text{ mΩ}$	BSB014N04LX3 G $R_{DS(on)}=1.4\text{ mΩ}$		BSC010N04LS $R_{DS(on)}=1.0\text{ mΩ}$	
		IRLS3034TRL PBF $R_{DS(on)}=1.7\text{ mΩ}$	IRLS3034TRL7P $R_{DS(on)}=1.4\text{ mΩ}$	IRLB3034PBF $R_{DS(on)}=1.7\text{ mΩ}$		IRL7486MTRPBF $R_{DS(on)}=1.4\text{ mΩ}$		BSC010N04LS6 $R_{DS(on)}=1.0\text{ mΩ}$	
		IRL40S212 $R_{DS(on)}=1.9\text{ mΩ}$		IRL40B212 $R_{DS(on)}=1.9\text{ mΩ}$				BSC010N04LST $R_{DS(on)}=1.0\text{ mΩ}$	
								BSC010N04LSI $R_{DS(on)}=1.05\text{ mΩ}$	
								BSC010N04LSC * $R_{DS(on)}=1.05\text{ mΩ}$	
								BSC014N04LST $R_{DS(on)}=1.4\text{ mΩ}$	
								BSC014N04LS $R_{DS(on)}=1.4\text{ mΩ}$	
								BSC014N04LSI $R_{DS(on)}=1.45\text{ mΩ}$	
								BSC016N04LS G $R_{DS(on)}=1.6\text{ mΩ}$	
							BSZ018N04LS6 $R_{DS(on)}=1.8\text{ mΩ}$	BSC018N04LS G $R_{DS(on)}=1.8\text{ mΩ}$	
								BSC019N04LS $R_{DS(on)}=1.9\text{ mΩ}$	
								BSC019N04LST $R_{DS(on)}=1.9\text{ mΩ}$	
2-4				IRL40B215 $R_{DS(on)}=2.7\text{ mΩ}$			BSZ021N04LS6 $R_{DS(on)}=2.1\text{ mΩ}$	BSC022N04LS $R_{DS(on)}=2.2\text{ mΩ}$	
							BSZ024N04LS6 $R_{DS(on)}=2.4\text{ mΩ}$	BSC022N04LS6 $R_{DS(on)}=2.2\text{ mΩ}$	
				IPP039N04L G $R_{DS(on)}=3.9\text{ mΩ}$			BSZ025N04LS $R_{DS(on)}=2.5\text{ mΩ}$	BSC026N04LS $R_{DS(on)}=2.6\text{ mΩ}$	
							BSZ028N04LS $R_{DS(on)}=2.8\text{ mΩ}$	BSC027N04LS G $R_{DS(on)}=2.7\text{ mΩ}$	
								BSC032N04LS $R_{DS(on)}=3.2\text{ mΩ}$	
4-10		IPD036N04L G $R_{DS(on)}=3.6\text{ mΩ}$	IRL1404S $R_{DS(on)}=4.0\text{ mΩ}$				BSZ034N04LS $R_{DS(on)}=3.4\text{ mΩ}$	BSC035N04LS G $R_{DS(on)}=3.5\text{ mΩ}$	
		IRLR31142TRPBF $R_{DS(on)}=4.5\text{ mΩ}$					BSZ040N04LS G $R_{DS(on)}=4.0\text{ mΩ}$	BSC050N04LS G $R_{DS(on)}=5.0\text{ mΩ}$	
							BSZ063N04LS6 $R_{DS(on)}=6.3\text{ mΩ}$	BSC059N04LS G $R_{DS(on)}=5.9\text{ mΩ}$	
								BSC059N04LS6 $R_{DS(on)}=5.9\text{ mΩ}$	
							BSZ097N04LS G $R_{DS(on)}=9.7\text{ mΩ}$	BSC093N04LS G $R_{DS(on)}=9.3\text{ mΩ}$	

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3) Coming soon

* Increased creepage distance



OptiMOS™ and StrongIRFET™ 60 V normal level

$R_{DS(on), max}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ⁺ PAK)	TO-263 (D ⁺ PAK 7-pin)	TO-262 (I ⁺ PAK)	TO-220	TO-220 FullPAK	TO-247
1-2			IPB010N06N ²⁾ $R_{DS(on)}=1.0\text{ mΩ}$				
			IRFS7530TRL7PP $R_{DS(on)}=1.4\text{ mΩ}$				
			IPB014N06N ²⁾ $R_{DS(on)}=1.4\text{ mΩ}$				
			IPB017N06N3 G $R_{DS(on)}=1.7\text{ mΩ}$				
		IRFS7530TRL7PBF $R_{DS(on)}=2.0\text{ mΩ}$	IRFS7534TRL7PP $R_{DS(on)}=1.95\text{ mΩ}$	IPI020N06N ²⁾ $R_{DS(on)}=2.0\text{ mΩ}$	IRFB7530PBF $R_{DS(on)}=2.0\text{ mΩ}$		IRFP7530PBF $R_{DS(on)}=2.0\text{ mΩ}$
2-4	IPD025N06N ²⁾ $R_{DS(on)}=2.5\text{ mΩ}$	IRFS7534TRL7PBF $R_{DS(on)}=2.4\text{ mΩ}$	IRFS3006TRL7PP $R_{DS(on)}=2.1\text{ mΩ}$		IPP020N06N ²⁾ $R_{DS(on)}=2.0\text{ mΩ}$		
		IRFS3006 $R_{DS(on)}=2.5\text{ mΩ}$		IPI024N06N3 G $R_{DS(on)}=2.4\text{ mΩ}$	IRFB7534PBF $R_{DS(on)}=2.4\text{ mΩ}$		
		IPB026N06N ²⁾ $R_{DS(on)}=2.6\text{ mΩ}$			IPP024N06N3 G ²⁾ $R_{DS(on)}=2.4\text{ mΩ}$		IRFP3006PBF $R_{DS(on)}=2.5\text{ mΩ}$
		IPB029N06N3 G $R_{DS(on)}=2.9\text{ mΩ}$		IPI029N06N ²⁾ $R_{DS(on)}=2.9\text{ mΩ}$	IPP029N06N ²⁾ $R_{DS(on)}=2.9\text{ mΩ}$	IPA029N06N ²⁾ $R_{DS(on)}=2.9\text{ mΩ}$	IRFP3206PBF $R_{DS(on)}=3.0\text{ mΩ}$
	IPD033N06N ²⁾ $R_{DS(on)}=3.3\text{ mΩ}$	IRFS3206 $R_{DS(on)}=3.0\text{ mΩ}$		IPI032N06N3 G $R_{DS(on)}=3.2\text{ mΩ}$	IPP032N06N3 G $R_{DS(on)}=3.2\text{ mΩ}$	IPA032N06N3 G $R_{DS(on)}=3.2\text{ mΩ}$	
	IPD034N06N3 G $R_{DS(on)}=3.4\text{ mΩ}$	IRFS7537TRL7PBF $R_{DS(on)}=3.3\text{ mΩ}$			IRFB7537PBF $R_{DS(on)}=3.3\text{ mΩ}$		IRFP7537PBF $R_{DS(on)}=3.3\text{ mΩ}$
	IPD038N06N3 G $R_{DS(on)}=3.8\text{ mΩ}$	IPB037N06N3 G $R_{DS(on)}=3.7\text{ mΩ}$			IPP040N06N3 G $R_{DS(on)}=4.0\text{ mΩ}$		
		IRFS3306 $R_{DS(on)}=4.2\text{ mΩ}$		IPI040N06N3 G $R_{DS(on)}=4.0\text{ mΩ}$	IPP040N06N ²⁾ $R_{DS(on)}=4.0\text{ mΩ}$	IPA040N06N ²⁾ $R_{DS(on)}=4.0\text{ mΩ}$	
4-10	IRFR7540TRPBF $R_{DS(on)}=4.8\text{ mΩ}$	IRFS7540TRL7PBF $R_{DS(on)}=5.1\text{ mΩ}$			IRFB7540PBF $R_{DS(on)}=5.1\text{ mΩ}$	IPA057N06N3 G $R_{DS(on)}=5.7\text{ mΩ}$	
	IPD053N06N ²⁾ $R_{DS(on)}=5.3\text{ mΩ}$	IPB054N06N3 G $R_{DS(on)}=5.4\text{ mΩ}$			IPP057N06N3 G ²⁾ $R_{DS(on)}=5.7\text{ mΩ}$		
		IPB057N06N ²⁾ $R_{DS(on)}=5.7\text{ mΩ}$			IRFB7545PBF $R_{DS(on)}=5.9\text{ mΩ}$		
	IRFR7546TRPBF $R_{DS(on)}=7.9\text{ mΩ}$	IRF1018ES $R_{DS(on)}=8.4\text{ mΩ}$			IPP060N06N ²⁾ $R_{DS(on)}=6.0\text{ mΩ}$	IPA060N06N ²⁾ $R_{DS(on)}=6.0\text{ mΩ}$	
	IPD088N06N3 G $R_{DS(on)}=8.8\text{ mΩ}$				IRF60B217 $R_{DS(on)}=9.0\text{ mΩ}$	IPA093N06N3 G $R_{DS(on)}=9.3\text{ mΩ}$	
	IRF60R217 $R_{DS(on)}=9.9\text{ mΩ}$	IPB090N06N3 G $R_{DS(on)}=9.0\text{ mΩ}$			IPP093N06N3 G $R_{DS(on)}=9.3\text{ mΩ}$		
>10		IRFS3806 $R_{DS(on)}=15.8\text{ mΩ}$					



OptiMOS™ and StrongIRFET™ 60 V normal level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	Bare die ($R_{DS(on)}$ typ.)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	TO-Leadless
<1					IPT007N06N ²⁾ $R_{DS(on)}=0.7\text{ mΩ}$ IPT012N06N ²⁾ $R_{DS(on)}=1.2\text{ mΩ}$
1-2	IPC218N06N3 $R_{DS(on)}=1.3\text{ mΩ}$	IRF7749L1TRPBF $R_{DS(on)}=1.5\text{ mΩ}$		BSC012N06NS $R_{DS(on)}=1.2\text{ mΩ}$ BSC014N06NS ²⁾ $R_{DS(on)}=1.4\text{ mΩ}$ BSC014N06NST ²⁾ $R_{DS(on)}=1.45\text{ mΩ}$ BSC016N06NST ²⁾ $R_{DS(on)}=1.6\text{ mΩ}$ BSC016N06NS ²⁾ $R_{DS(on)}=1.6\text{ mΩ}$ BSC019N06NS ²⁾ $R_{DS(on)}=1.9\text{ mΩ}$	
2-4		IRF7748L1TRPBF $R_{DS(on)}=2.2\text{ mΩ}$		BSC028N06NS ²⁾ $R_{DS(on)}=2.8\text{ mΩ}$ BSC028N06NST ²⁾ $R_{DS(on)}=2.8\text{ mΩ}$ BSC031N06NS3 G $R_{DS(on)}=3.1\text{ mΩ}$	
		BSB028N06NN3 G $R_{DS(on)}=2.8\text{ mΩ}$		IRFH7085TRPBF $R_{DS(on)}=3.2\text{ mΩ}$ BSC034N06NS ²⁾ $R_{DS(on)}=3.4\text{ mΩ}$ BSC039N06NS ²⁾ $R_{DS(on)}=3.9\text{ mΩ}$	
		IRF60DM206 $R_{DS(on)}=2.9\text{ mΩ}$			
		IRF7580MTRPBF $R_{DS(on)}=3.6\text{ mΩ}$			
4-10		IRF6648 $R_{DS(on)}=7.0\text{ mΩ}$ IRF6674 $R_{DS(on)}=11.0\text{ mΩ}$	BSZ042N06NS ²⁾ $R_{DS(on)}=4.2\text{ mΩ}$ BSZ068N06NS ²⁾ $R_{DS(on)}=6.8\text{ mΩ}$ BSZ100N06NS ²⁾ $R_{DS(on)}=10.0\text{ mΩ}$	IRLH5036TRPBF $R_{DS(on)}=4.4\text{ mΩ}$ IRFH7545TRPBF $R_{DS(on)}=5.2\text{ mΩ}$ BSC066N06NS ²⁾ $R_{DS(on)}=6.6\text{ mΩ}$ BSC076N06NS3 G $R_{DS(on)}=7.6\text{ mΩ}$ BSC097N06NS ²⁾ $R_{DS(on)}=9.7\text{ mΩ}$ BSC097N06NST ²⁾ $R_{DS(on)}=9.7\text{ mΩ}$ BSC110N06NS3 G $R_{DS(on)}=11.0\text{ mΩ}$	
>10			BSZ110N06NS3 G $R_{DS(on)}=11.0\text{ mΩ}$		



OptiMOS™ and StrongIRFET™ 60 V logic level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-262 (i ² PAK)	TO-220	Bare die ($R_{DS(on)}$ typ.)	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	SOT-23
1-2		IPB019N06L3 G $R_{DS(on)}=1.9\text{ mΩ}$	IPB016N06L3 G $R_{DS(on)}=1.6\text{ mΩ}$			IPC218N06L3 $R_{DS(on)}=1.2\text{ mΩ}$			BSC014N06LS5 $R_{DS(on)}=1.4\text{ mΩ}$	
		IRL60S216 $R_{DS(on)}=1.95\text{ mΩ}$		IRL60SL216 $R_{DS(on)}=1.95\text{ mΩ}$	IRL60B216 $R_{DS(on)}=1.9\text{ mΩ}$					
2-4		IRLS3036TRL PBF $R_{DS(on)}=2.4\text{ mΩ}$			IRLB3036PBF $R_{DS(on)}=2.4\text{ mΩ}$				BSC027N06LS5 $R_{DS(on)}=2.7\text{ mΩ}$ BSC028N06LS3 G $R_{DS(on)}=2.8\text{ mΩ}$	
	IPD031N06L3 G $R_{DS(on)}=3.1\text{ mΩ}$ IPD048N06L3 G $R_{DS(on)}=4.8\text{ mΩ}$ IRLR3636TRPBF $R_{DS(on)}=6.8\text{ mΩ}$	IPB034N06L3 G $R_{DS(on)}=3.4\text{ mΩ}$			IPP037N06L3 G $R_{DS(on)}=3.7\text{ mΩ}$ IPP052N06L3 G $R_{DS(on)}=5.2\text{ mΩ}$			BSZ040N06LS5 $R_{DS(on)}=4.0\text{ mΩ}$ BSZ065N06LS5 $R_{DS(on)}=6.5\text{ mΩ}$ BSZ067N06LS3 G $R_{DS(on)}=6.7\text{ mΩ}$ BSZ099N06LS5 $R_{DS(on)}=9.9\text{ mΩ}$ BSZ100N06LS3 G $R_{DS(on)}=10.0\text{ mΩ}$	IRLH5036TRPBF $R_{DS(on)}=4.4\text{ mΩ}$ BSC065N06LS5 $R_{DS(on)}=6.5\text{ mΩ}$ BSC067N06LS3 G $R_{DS(on)}=6.7\text{ mΩ}$ BSC094N06LS5 $R_{DS(on)}=9.4\text{ mΩ}$ BSC100N06LS3 G $R_{DS(on)}=10.0\text{ mΩ}$	
4-10		IPB081N06L3 G $R_{DS(on)}=8.1\text{ mΩ}$		IPI084N06L3 G $R_{DS(on)}=8.4\text{ mΩ}$	IPP084N06L3 G $R_{DS(on)}=8.4\text{ mΩ}$					
>10	IPD350N06L G $R_{DS(on)}=35.0\text{ mΩ}$						IRL60HS118 $R_{DS(on)}=17.0\text{ mΩ}$			IRLML0060 $R_{DS(on)}=92\text{ mΩ}$ IRLML2060 $R_{DS(on)}=480\text{ mΩ}$

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2) 6 V rated ($R_{DS(on)}$ also specified @ $V_{GS} = 6\text{ V}$)



OptiMOS™ and StrongIRFET™ 75 V normal level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-220	TO-247	Bare die ($R_{DS(on)}$ typ.)	DirectFET™	SuperSO8
1-2		IPB020NE7N3 G $R_{DS(on)}=2.0\text{ mΩ}$	IRFS7730TRL7PP $R_{DS(on)}=2.0\text{ mΩ}$		IRFP7718PBF $R_{DS(on)}=1.8\text{ mΩ}$	IPC302NE7N3 $R_{DS(on)}=1.2\text{ mΩ}$		
2-4		IRFS7730TRL7PBF $R_{DS(on)}=2.6\text{ mΩ}$		IPP023NE7N3 G $R_{DS(on)}=2.3\text{ mΩ}$				
		IPB031NE7N3 G $R_{DS(on)}=3.1\text{ mΩ}$	IRFS7734TRL7PP $R_{DS(on)}=3.05\text{ mΩ}$	IRFB7730PBF $R_{DS(on)}=2.6\text{ mΩ}$				BSC036NE7NS3 G $R_{DS(on)}=3.6\text{ mΩ}$
		IRFS7734TRL7PBF $R_{DS(on)}=3.5\text{ mΩ}$		IPP034NE7N3 G $R_{DS(on)}=3.4\text{ mΩ}$				
4-10		IPB049NE7N3 G $R_{DS(on)}=4.9\text{ mΩ}$		IPP052NE7N3 G $R_{DS(on)}=5.2\text{ mΩ}$				BSC042NE7NS3 G $R_{DS(on)}=4.2\text{ mΩ}$
		IRFS7762TRL7PBF $R_{DS(on)}=6.7\text{ mΩ}$		IPP062NE7N3 G $R_{DS(on)}=6.2\text{ mΩ}$			IRF7780MTRPBF $R_{DS(on)}=5.7\text{ mΩ}$	
	IRFR7740TRPBF $R_{DS(on)}=7.2\text{ mΩ}$			IRFB7740PBF $R_{DS(on)}=7.3\text{ mΩ}$				
		IRFS7787TRL7PBF $R_{DS(on)}=8.4\text{ mΩ}$		IRFB7787PBF $R_{DS(on)}=8.4\text{ mΩ}$				IRFH7787TRPBF $R_{DS(on)}=8.0\text{ mΩ}$
>10	IRFR7746TRPBF $R_{DS(on)}=11.2\text{ mΩ}$			IRFB7746PBF $R_{DS(on)}=10.6\text{ mΩ}$			BSF450NE7NH3 ¹⁾ $R_{DS(on)}=45.0\text{ mΩ}$	



OptiMOS™ and StrongIRFET™ 80 V normal level – logic level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-262 (I ² PAK)	TO-220	TO-220 FullPAK	Bare die ($R_{DS(on)}$ typ.)	DirectFET™	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	TO-Leadless
1-2		IPB017N08N5 $R_{DS(on)}=1.7\text{ mΩ}$	IPB015N08N5 $R_{DS(on)}=1.5\text{ mΩ}$				IPC302N08N3 $R_{DS(on)}=1.2\text{ mΩ}$					IPT012N08N5 $R_{DS(on)}=1.2\text{ mΩ}$
		IPB020N08N5 $R_{DS(on)}=2.0\text{ mΩ}$	IPB019N08N3 G $R_{DS(on)}=1.9\text{ mΩ}$		IPP020N08N5 $R_{DS(on)}=2.0\text{ mΩ}$						BSC021N08NS5 $R_{DS(on)}=2.1\text{ mΩ}$	IPT019N08N5 $R_{DS(on)}=1.9\text{ mΩ}$
2-4		IPB024N08N5 $R_{DS(on)}=2.4\text{ mΩ}$			IPP023N08N5 $R_{DS(on)}=2.3\text{ mΩ}$						BSC025N08LS5 $R_{DS(on)}=2.5\text{ mΩ}$	
		IPB025N08N3 G $R_{DS(on)}=2.5\text{ mΩ}$	IPB030N08N3 G $R_{DS(on)}=3.0\text{ mΩ}$		IPP027N08N5 $R_{DS(on)}=2.7\text{ mΩ}$						BSC026N08NS5 $R_{DS(on)}=2.6\text{ mΩ}$	
					IPP028N08N3 G $R_{DS(on)}=2.8\text{ mΩ}$	IPA028N08N3 G $R_{DS(on)}=2.8\text{ mΩ}$					BSC030N08NS5 $R_{DS(on)}=3.0\text{ mΩ}$	IPT029N08N5 $R_{DS(on)}=2.9\text{ mΩ}$
		IPB031N08N5 $R_{DS(on)}=3.1\text{ mΩ}$			IPP034N08N5 $R_{DS(on)}=3.4\text{ mΩ}$						BSC037N08NS5 $R_{DS(on)}=3.7\text{ mΩ}$	
											BSC037N08NS5T $R_{DS(on)}=3.7\text{ mΩ}$	
		IPB035N08N3 G $R_{DS(on)}=3.5\text{ mΩ}$		IPI037N08N3 G $R_{DS(on)}=3.7\text{ mΩ}$	IPP037N08N3 G $R_{DS(on)}=3.7\text{ mΩ}$	IPA037N08N3 G $R_{DS(on)}=3.7\text{ mΩ}$					BSC040N08NS5 $R_{DS(on)}=4.0\text{ mΩ}$	
4-10	IPD046N08N5 $R_{DS(on)}=4.6\text{ mΩ}$	IPB049N08N5 $R_{DS(on)}=4.9\text{ mΩ}$			IPP052N08N5 $R_{DS(on)}=5.2\text{ mΩ}$			BSB044N08NN3 G $R_{DS(on)}=4.4\text{ mΩ}$			BSC047N08NS3 G $R_{DS(on)}=4.7\text{ mΩ}$	
	IPD053N08N3 G $R_{DS(on)}=5.3\text{ mΩ}$	IPB054N08N3 G $R_{DS(on)}=5.4\text{ mΩ}$			IPP057N08N3 G $R_{DS(on)}=5.7\text{ mΩ}$	IPA057N08N3 G $R_{DS(on)}=5.7\text{ mΩ}$					BSC052N08NS5 $R_{DS(on)}=5.2\text{ mΩ}$	
		IPB067N08N3 G $R_{DS(on)}=6.7\text{ mΩ}$									BSC057N08NS3 G $R_{DS(on)}=5.7\text{ mΩ}$	
										BSZ070N08LS5 $R_{DS(on)}=7.0\text{ mΩ}$	BSC061N08NS5 $R_{DS(on)}=6.1\text{ mΩ}$	
										BSZ075N08NS5 $R_{DS(on)}=7.5\text{ mΩ}$	BSC072N08NS5 $R_{DS(on)}=7.2\text{ mΩ}$	
>10	IPD096N08N3 G $R_{DS(on)}=9.6\text{ mΩ}$				IPP100N08N3 G $R_{DS(on)}=9.7\text{ mΩ}$					BSZ084N08NS5 $R_{DS(on)}=8.4\text{ mΩ}$	BSC117N08NS5 $R_{DS(on)}=11.7\text{ mΩ}$	
								BSB104N08NP3 $R_{DS(on)}=10.4\text{ mΩ}$	IRL80HS120 $R_{DS(on)}=32.0\text{ mΩ}$	BSZ110N08NS5 $R_{DS(on)}=11.0\text{ mΩ}$	BSC123N08NS3 $R_{DS(on)}=12.3\text{ mΩ}$	
	IPD135N08N3 G $R_{DS(on)}=13.5\text{ mΩ}$									BSZ123N08NS3 G $R_{DS(on)}=12.3\text{ mΩ}$	BSC340N08NS3 G $R_{DS(on)}=34.0\text{ mΩ}$	

OptiMOS™ and StrongIRFET™ 100 V normal level



$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-262 (I ² PAK)	TO-220	TO-220 FullPAK	TO-247
1-2		IPB020N10N5 $R_{DS(on)}=2.0\text{ mΩ}$	IPB017N10N5 $R_{DS(on)}=1.7\text{ mΩ}$				IRF100P218 $R_{DS(on)}=1.1\text{ mΩ}$
		IPB020N10N5LF $R_{DS(on)}=2.0\text{ mΩ}$	IPB017N10N5LF $R_{DS(on)}=1.7\text{ mΩ}$				IRF100P219 $R_{DS(on)}=2.1\text{ mΩ}$
2-4		IPB027N10N3 G $R_{DS(on)}=2.7\text{ mΩ}$	IPB024N10N5 $R_{DS(on)}=2.4\text{ mΩ}$		IPP023N10N5 $R_{DS(on)}=2.3\text{ mΩ}$		IRFP4468PBF $R_{DS(on)}=2.6\text{ mΩ}$
		IPB027N10N5 $R_{DS(on)}=2.7\text{ mΩ}$	IPB025N10N3 G $R_{DS(on)}=2.5\text{ mΩ}$	IPI030N10N3 G $R_{DS(on)}=3.0\text{ mΩ}$	IPP030N10N3 G $R_{DS(on)}=3.0\text{ mΩ}$	IPA030N10N3 G $R_{DS(on)}=3.0\text{ mΩ}$	
		IPB033N10N5LF $R_{DS(on)}=3.3\text{ mΩ}$	IPB032N10N5 $R_{DS(on)}=3.2\text{ mΩ}$		IPP030N10N5 $R_{DS(on)}=3.0\text{ mΩ}$		
			IPB039N10N3 G $R_{DS(on)}=3.9\text{ mΩ}$		IPP039N10N5 $R_{DS(on)}=3.9\text{ mΩ}$		
4-10	IPD050N10N5 $R_{DS(on)}=5.0\text{ mΩ}$	IPB042N10N3 G $R_{DS(on)}=4.2\text{ mΩ}$		IPI045N10N3 G $R_{DS(on)}=4.5\text{ mΩ}$	IRFB4110PBF $R_{DS(on)}=4.5\text{ mΩ}$	IPA045N10N3 G $R_{DS(on)}=4.5\text{ mΩ}$	IRFP4110PBF $R_{DS(on)}=4.5\text{ mΩ}$
	IPD068N10N3 G $R_{DS(on)}=6.8\text{ mΩ}$	IRFS4010TRL PBF $R_{DS(on)}=4.7\text{ mΩ}$			IPP045N10N3 G $R_{DS(on)}=4.5\text{ mΩ}$	IPA083N10N5 $R_{DS(on)}=8.3\text{ mΩ}$	IRFP4310ZPBF $R_{DS(on)}=6.0\text{ mΩ}$
		IPB065N10N3 G $R_{DS(on)}=6.5\text{ mΩ}$			IRFB4310ZPBF $R_{DS(on)}=6.0\text{ mΩ}$	IPA086N10N3 G $R_{DS(on)}=8.6\text{ mΩ}$	
		IRFS4310ZTRL PBF $R_{DS(on)}=7.0\text{ mΩ}$					
				IPI072N10N3 G $R_{DS(on)}=7.2\text{ mΩ}$	IPP072N10N3 G $R_{DS(on)}=7.2\text{ mΩ}$		
	IPD082N10N3 G $R_{DS(on)}=8.2\text{ mΩ}$				IPP083N10N5 $R_{DS(on)}=8.3\text{ mΩ}$		
		IPB083N10N3 G $R_{DS(on)}=8.3\text{ mΩ}$		IPI086N10N3 G $R_{DS(on)}=8.6\text{ mΩ}$	IPP086N10N3 G $R_{DS(on)}=8.6\text{ mΩ}$		
		IRFS4410ZTRL PBF $R_{DS(on)}=9.0\text{ mΩ}$			IRFS4410ZTRL PBF $R_{DS(on)}=9.0\text{ mΩ}$		IRFP4410ZPBF $R_{DS(on)}=9.0\text{ mΩ}$
10-25	IPD122N10N3 G $R_{DS(on)}=12.2\text{ mΩ}$						
	IPD12CN10N G $R_{DS(on)}=12.4\text{ mΩ}$	IPB123N10N3 G $R_{DS(on)}=12.3\text{ mΩ}$					
	IRFR4510TRPBF $R_{DS(on)}=13.9\text{ mΩ}$	IRFS4510TRL PBF $R_{DS(on)}=13.9\text{ mΩ}$					
	IPD180N10N3 G $R_{DS(on)}=18.0\text{ mΩ}$			IPI180N10N3 G $R_{DS(on)}=18.0\text{ mΩ}$			
	IPD25CN10N G $R_{DS(on)}=25.0\text{ mΩ}$						
>25	IPD33CN10N G $R_{DS(on)}=33.0\text{ mΩ}$						
	IPD78CN10N G $R_{DS(on)}=78.0\text{ mΩ}$						



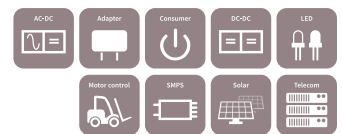
OptiMOS™ and StrongIRFET™ 100 V normal level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	Bare die ($R_{DS(on)}$ typ.)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	SO-8	TO-Leadless
1-2	IPC302N10N3 $R_{DS(on)}=1.7\text{ mΩ}$					IPT015N10N5 $R_{DS(on)}=1.5\text{ mΩ}$
	IPC313N10N3R $R_{DS(on)}=1.9\text{ mΩ}$			BSC027N10NS5 $R_{DS(on)}=2.7\text{ mΩ}$		IPT020N10N3 $R_{DS(on)}=2.0\text{ mΩ}$
						IPT020N10N5 $R_{DS(on)}=2.0\text{ mΩ}$
2-4	IPC26N10NR $R_{DS(on)}=3.2\text{ mΩ}$	IRF7769L1TRPBF $R_{DS(on)}=3.5\text{ mΩ}$		BSC035N10NS5 $R_{DS(on)}=3.5\text{ mΩ}$		IPT026N10N5 $R_{DS(on)}=2.6\text{ mΩ}$
	IPC173N10N3 $R_{DS(on)}=3.6\text{ mΩ}$			BSC040N10NS5 $R_{DS(on)}=4.0\text{ mΩ}$		
4-10		IRF100DM116 ³⁾ $R_{DS(on)}=4.3\text{ mΩ}$		BSC050N10NS5 $R_{DS(on)}=5.0\text{ mΩ}$		
		BSB056N10NN3 G $R_{DS(on)}=5.6\text{ mΩ}$		BSC060N10NS3 G $R_{DS(on)}=6.0\text{ mΩ}$		
				BSC070N10NS3 G $R_{DS(on)}=7.0\text{ mΩ}$		
				BSC070N10NS5 $R_{DS(on)}=7.0\text{ mΩ}$		
				IRFH5010TRPBF $R_{DS(on)}=9.0\text{ mΩ}$		
			BSZ097N10NS5 $R_{DS(on)}=9.7\text{ mΩ}$	BSC098N10NS5 $R_{DS(on)}=9.8\text{ mΩ}$		
10-25				BSC109N10NS3 G $R_{DS(on)}=10.9\text{ mΩ}$		
				BSC118N10NS G $R_{DS(on)}=11.8\text{ mΩ}$		
		BSF134N10NJ3 G ¹⁾ $R_{DS(on)}=13.4\text{ mΩ}$		IRFH7110TRPBF $R_{DS(on)}=13.5\text{ mΩ}$		
	IPC045N10N3 $R_{DS(on)}=15.2\text{ mΩ}$		BSZ160N10NS3 G $R_{DS(on)}=16.0\text{ mΩ}$	BSC160N10NS3 G $R_{DS(on)}=16.0\text{ mΩ}$		
		IRF6662TRPBF $R_{DS(on)}=22.0\text{ mΩ}$		BSC196N10NS G $R_{DS(on)}=19.6\text{ mΩ}$	IRF7853TRPBF $R_{DS(on)}=18.0\text{ mΩ}$	
>25		IRF6645TRPBF $R_{DS(on)}=35.0\text{ mΩ}$	BSZ440N10NS3 G $R_{DS(on)}=44.0\text{ mΩ}$	BSC252N10NSF G $R_{DS(on)}=25.2\text{ mΩ}$		
		IRF7665S2TRPBF $R_{DS(on)}=62.0\text{ mΩ}$		BSC440N10NS3 G $R_{DS(on)}=44.0\text{ mΩ}$		
2 x 75				BSC750N10ND G $R_{DS(on)}=75.0\text{ mΩ; dual}$		
2 x 195			IRFHM792TRPBF $R_{DS(on)}=195.0\text{ mΩ}$			

OptiMOS™ and StrongIRFET™ 100 V logic level



$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-220	Bare die ($R_{DS(on)}$ typ.)	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	SOT-23
2-4			IRLS4030TRL7PP $R_{DS(on)}=3.9\text{ mΩ}$					BSC034N10LS5 $R_{DS(on)}=3.4\text{ mΩ}$	
4-10		IRLS4030TRL7PP $R_{DS(on)}=4.3\text{ mΩ}$		IRLB4030PBF $R_{DS(on)}=4.3\text{ mΩ}$			BSZ096N10LS5 $R_{DS(on)}=9.6\text{ mΩ}$		
10-25				IPP12CN10L G $R_{DS(on)}=12.0\text{ mΩ}$	IPC045N10L3 ²⁾ $R_{DS(on)}=16.0\text{ mΩ}$		BSZ146N10LS5 $R_{DS(on)}=14.6\text{ mΩ}$	BSC123N10LS G $R_{DS(on)}=12.3\text{ mΩ}$	
	IRLR3110ZTRPBF $R_{DS(on)}=14.0\text{ mΩ}$						BSZ150N10LS3 $R_{DS(on)}=15.0\text{ mΩ}$	BSC146N10LS5 $R_{DS(on)}=14.6\text{ mΩ}$	
>25					IPC020N10L3 ²⁾ $R_{DS(on)}=42.0\text{ mΩ}$	IRL100HS121 $R_{DS(on)}=42.0\text{ mΩ}$		BSC265N10LSF G $R_{DS(on)}=26.5\text{ mΩ}$	IRLML0100 $R_{DS(on)}=220\text{ mΩ}$



OptiMOS™ and StrongIRFET™ 120 V normal level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-262 (IPAK)	TO-220	Bare die ($R_{DS(on)}$ typ.)	PQFN 3.3 x 3.3	SuperSO8
2-4						IPC302N12N3 $R_{DS(on)}=2.5\text{ mΩ}$		
						IPC26N12N $R_{DS(on)}=3.0\text{ mΩ}$		
		IPB038N12N3 G $R_{DS(on)}=3.8\text{ mΩ}$	IPB036N12N3 G $R_{DS(on)}=3.6\text{ mΩ}$			IPC26N12NR $R_{DS(on)}=3.2\text{ mΩ}$		
4-10				IPI041N12N3 G $R_{DS(on)}=4.1\text{ mΩ}$	IPP041N12N3 G $R_{DS(on)}=4.1\text{ mΩ}$			
					IPP048N12N3 G $R_{DS(on)}=4.8\text{ mΩ}$			
				IPI076N12N3 G $R_{DS(on)}=7.6\text{ mΩ}$	IPP076N12N3 G $R_{DS(on)}=7.6\text{ mΩ}$			BSC077N12NS3 G $R_{DS(on)}=7.7\text{ mΩ}$
10-25	IPD110N12N3 G $R_{DS(on)}=11.0\text{ mΩ}$				IPP114N12N3 G $R_{DS(on)}=11.4\text{ mΩ}$			
		IPB144N12N3 G $R_{DS(on)}=14.4\text{ mΩ}$		IPI147N12N3 G $R_{DS(on)}=14.7\text{ mΩ}$	IPP147N12N3 G $R_{DS(on)}=14.7\text{ mΩ}$		BSZ240N12NS3 G $R_{DS(on)}=24.0\text{ mΩ}$	BSC190N12NS3 G $R_{DS(on)}=19.0\text{ mΩ}$



OptiMOST™ and StrongIRFET™ 135-150 V normal level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	Bare die ($R_{DS(on)}$ typ.)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	TO-Leadless
4-10	IPC302N15N3 $R_{DS(on)}=4.9\text{ mΩ}$ IPC300N15N3R $R_{DS(on)}=4.9\text{ mΩ}$			BSC093N15NS5 $R_{DS(on)}=9.3\text{ mΩ}$	IPT059N15N3 $R_{DS(on)}=5.9\text{ mΩ}$
10-25		IRF7779L2TRPBF ⁵⁾ $R_{DS(on)}=11.0\text{ mΩ}$		BSC110N15NS5 $R_{DS(on)}=11.0\text{ mΩ}$ BSC160N15NS5 $R_{DS(on)}=16.0\text{ mΩ}$ BSC190N15NS3 G $R_{DS(on)}=19.0\text{ mΩ}$	
>25		BSB165N15NZ3 G $R_{DS(on)}=16.5\text{ mΩ}$ BSB280N15NZ3 G $R_{DS(on)}=28.0\text{ mΩ}$ IRF6643TRPBF $R_{DS(on)}=34.5\text{ mΩ}$ IRF6775MTRPBF $R_{DS(on)}=56.0\text{ mΩ}$	BSZ300N15NS5 $R_{DS(on)}=30.0\text{ mΩ}$ BSZ520N15NS3 G $R_{DS(on)}=52.0\text{ mΩ}$ BSZ900N15NS3 G $R_{DS(on)}=90.0\text{ mΩ}$	BSC360N15NS3 G $R_{DS(on)}=36.0\text{ mΩ}$ BSC520N15NS3 G $R_{DS(on)}=52.0\text{ mΩ}$	



OptiMOST™ and StrongIRFET™ 135-150 V normal level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-pin)	TO-263 (D ² PAK 7-pin+)	TO-251/ TO-251 Short Lead (IPAK/IPAK Short Lead)	TO-262 (I ² PAK)	TO-220	TO-220 FullIPAK	TO-247
4-10		IPB048N15N5 $R_{DS(on)}=4.8\text{ mΩ}$ IPB048N15N5LF $R_{DS(on)}=4.8\text{ mΩ}$ IPB072N15N3 G $R_{DS(on)}=7.2\text{ mΩ}$ IPB073N15N5 $R_{DS(on)}=7.3\text{ mΩ}$ IPB083N15N5LF $R_{DS(on)}=8.3\text{ mΩ}$ IRF135S203 ⁵⁾ $R_{DS(on)}=8.4\text{ mΩ}$	IPB044N15N5 $R_{DS(on)}=4.4\text{ mΩ}$ IRF135SA204 ⁵⁾ $R_{DS(on)}=5.9\text{ mΩ}$ IPB060N15N5 $R_{DS(on)}=6.0\text{ mΩ}$ IPB065N15N3 G $R_{DS(on)}=6.5\text{ mΩ}$		IRF135SA204 $R_{DS(on)}=5.9\text{ mΩ}$	IPI051N15N5 $R_{DS(on)}=5.1\text{ mΩ}$ IPI075N15N3 G $R_{DS(on)}=7.5\text{ mΩ}$ IPI076N15N5 $R_{DS(on)}=7.6\text{ mΩ}$	IPP051N15N5 ²⁾ $R_{DS(on)}=5.1\text{ mΩ}$ IPP075N15N3 G $R_{DS(on)}=7.5\text{ mΩ}$ IPP076N15N5 $R_{DS(on)}=7.6\text{ mΩ}$		IRF150P220 $R_{DS(on)}=2.5\text{ mΩ}$ IRF150P221 $R_{DS(on)}=4.8\text{ mΩ}$ IRFP4568PBF $R_{DS(on)}=5.9\text{ mΩ}$
10-25		IRFS4115TRL7PP $R_{DS(on)}=11.8\text{ mΩ}$ IRFS4321 $R_{DS(on)}=15.0\text{ mΩ}$ IPD200N15N3 G $R_{DS(on)}=20.0\text{ mΩ}$	IRFS4115TRL7PP $R_{DS(on)}=11.8\text{ mΩ}$ IRFS4321TRL7PP $R_{DS(on)}=14.7\text{ mΩ}$			IPI111N15N3 G $R_{DS(on)}=11.1\text{ mΩ}$	IPP111N15N3 G $R_{DS(on)}=11.1\text{ mΩ}$ IRFB4321PBF $R_{DS(on)}=15.0\text{ mΩ}$ IPP200N15N3 G ²⁾ $R_{DS(on)}=20.0\text{ mΩ}$	IPA105N15N3 G $R_{DS(on)}=10.5\text{ mΩ}$	IRFP4321PBF $R_{DS(on)}=15.5\text{ mΩ}$
>25		IRFS4615PBF $R_{DS(on)}=42.0\text{ mΩ}$ IRFR4615 $R_{DS(on)}=42.0\text{ mΩ}$ IPD530N15N3 G $R_{DS(on)}=53.0\text{ mΩ}$	IRFS5615PBF $R_{DS(on)}=42.0\text{ mΩ}$ IPB530N15N3 G $R_{DS(on)}=53.0\text{ mΩ}$		IRFU4615PBF $R_{DS(on)}=42.0\text{ mΩ}$	IPI530N15N3 G ²⁾ $R_{DS(on)}=53.0\text{ mΩ}$	IRFB4615PBF $R_{DS(on)}=39.0\text{ mΩ}$ IRFB5615PBF $R_{DS(on)}=39.0\text{ mΩ}$ IPP530N15N3 G ²⁾ $R_{DS(on)}=53.0\text{ mΩ}$ IRFB4019PBF $R_{DS(on)}=95.0\text{ mΩ}$		

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2) 8 V rated ($R_{DS(on)}$ also specified @ $V_{GS} = 8\text{ V}$)

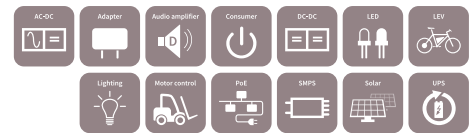
3) In development

5) 135 V



OptiMOS™ and StrongIRFET™ 200 V normal level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK+)	TO-262 (IPAK)	TO-220	TO-247
4-10						IRF200P222 $R_{DS(on)}=6.6\text{ mΩ}$
						IRFP4668PBF $R_{DS(on)}=9.7\text{ mΩ}$
10-25		IPB107N20N3 G $R_{DS(on)}=10.7\text{ mΩ}$	IRF200S234 $R_{DS(on)}=16.9\text{ mΩ}$	IP110N20N3 G $R_{DS(on)}=11.0\text{ mΩ}$	IPP110N20N3 G $R_{DS(on)}=11.0\text{ mΩ}$	IRF200P223 $R_{DS(on)}=11.5\text{ mΩ}$
		IPB107N20NA ⁴⁾ $R_{DS(on)}=10.7\text{ mΩ}$				
		IPB110N20N3LF $R_{DS(on)}=11.0\text{ mΩ}$			IPP120N20NFD $R_{DS(on)}=12.0\text{ mΩ}$	IRFP4127PBF $R_{DS(on)}=21.0\text{ mΩ}$
		IPB117N20NFD $R_{DS(on)}=11.7\text{ mΩ}$			IRFB4127PBF $R_{DS(on)}=20.0\text{ mΩ}$	IRFP4227PBF $R_{DS(on)}=25.0\text{ mΩ}$
		IPB156N22NFD ²⁾ $R_{DS(on)}=15.6\text{ mΩ}$				
		IRFS4127TRL PBF $R_{DS(on)}=22.0\text{ mΩ}$				
>25		IRFS4227TRL PBF $R_{DS(on)}=26.0\text{ mΩ}$			IRFB4227PBF $R_{DS(on)}=26.0\text{ mΩ}$	
	IPD320N20N3 G $R_{DS(on)}=32.0\text{ mΩ}$	IPB320N20N3 G $R_{DS(on)}=32.0\text{ mΩ}$		IP1320N20N3 G $R_{DS(on)}=32.0\text{ mΩ}$	IPP320N20N3 G $R_{DS(on)}=32.0\text{ mΩ}$	
					IRFB4620PBF $R_{DS(on)}=72.5\text{ mΩ}$	
	IRFR4620TRL PBF $R_{DS(on)}=78.0\text{ mΩ}$	IRFS4620TRL PBF $R_{DS(on)}=78.0\text{ mΩ}$			IRFB5620PBF $R_{DS(on)}=72.5\text{ mΩ}$	
		IRFS4020TRL PBF $R_{DS(on)}=105.0\text{ mΩ}$			IRFB4020PBF $R_{DS(on)}=100.0\text{ mΩ}$	
					IRF200B211 $R_{DS(on)}=170.0\text{ mΩ}$	



OptiMOS™ and StrongIRFET™ 200 V normal level

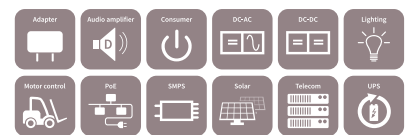
$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	Bare die ($R_{DS(on)}$ typ.)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	SO-8	TO-Leadless	TO-247
4-10	IPC300N20N3 $R_{DS(on)}=9.2\text{ mΩ}$						IRF200P222 $R_{DS(on)}=6.6\text{ mΩ}$
	IPC302N20N3 $R_{DS(on)}=9.2\text{ mΩ}$						
10-25	IPC302N20NFD $R_{DS(on)}=9.4\text{ mΩ}$			BSC220N20NSFD $R_{DS(on)}=22.0\text{ mΩ}$		IP111N20NFD $R_{DS(on)}=11.1\text{ mΩ}$	IRF200P223 $R_{DS(on)}=11.5\text{ mΩ}$
>25				BSC320N20NS3 G $R_{DS(on)}=32.0\text{ mΩ}$			
				BSC350N20NSFD $R_{DS(on)}=35.0\text{ mΩ}$			
				BSC500N20NS3G $R_{DS(on)}=50.0\text{ mΩ}$			
	IRF6641TRPBF $R_{DS(on)}=59.9\text{ mΩ}$			IRFH5020 $R_{DS(on)}=55.0\text{ mΩ}$			
			BSZ900N20NS3 G $R_{DS(on)}=90.0\text{ mΩ}$	BSC900N20NS3 G $R_{DS(on)}=90.0\text{ mΩ}$	IRF7820TRPBF $R_{DS(on)}=78.0\text{ mΩ}$		
	IRF6785TRPBF $R_{DS(on)}=100.0\text{ mΩ}$		BSZ12DN20NS3 G $R_{DS(on)}=125.0\text{ mΩ}$	BSC12DN20NS3 G $R_{DS(on)}=125.0\text{ mΩ}$			
			BSZ22DN20NS3 G $R_{DS(on)}=225.0\text{ mΩ}$	BSC22DN20NS3 G $R_{DS(on)}=225.0\text{ mΩ}$			

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2) 220 V rated

3) In development

4) Part qualified according to AEC Q101



OptiMOS™ and StrongIRFET™ 250 V normal level

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-262 (I ² PAK)	TO-220	TO-247	Bare die ($R_{DS(on)}$ typ.)	PQFN 3.3 x 3.3	SuperSO8	TO-Leadless
10-25		IPB200N25N3 G $R_{DS(on)}=20.0\text{ mΩ}$	IPI200N25N3 G $R_{DS(on)}=20.0\text{ mΩ}$	IPP200N25N3 G $R_{DS(on)}=20.0\text{ mΩ}$	IRF250P224 $R_{DS(on)}=12.0\text{ mΩ}$				
				IPP220N25NFD $R_{DS(on)}=22.0\text{ mΩ}$	IRFP4768PBF $R_{DS(on)}=17.5\text{ mΩ}$	IPC302N25N3 $R_{DS(on)}=16.0\text{ mΩ}$			IPT210N25NFD $R_{DS(on)}=21.0\text{ mΩ}$
					IRF250P225 $R_{DS(on)}=22.0\text{ mΩ}$				
>25								BSC430N25NSFD $R_{DS(on)}=43.0\text{ mΩ}$	
		IRFS4229TRL PBF $R_{DS(on)}=48.0\text{ mΩ}$		IRFB4332PBF $R_{DS(on)}=33.0\text{ mΩ}$	IRFP4332PBF $R_{DS(on)}=33.0\text{ mΩ}$			BSC600N25NS3 G $R_{DS(on)}=60.0\text{ mΩ}$	
								BSC670N25NSFD $R_{DS(on)}=67.0\text{ mΩ}$	
	IPD600N25N3 G $R_{DS(on)}=60.0\text{ mΩ}$	IPB600N25N3 G $R_{DS(on)}=60.0\text{ mΩ}$	IPI600N25N3 G $R_{DS(on)}=60.0\text{ mΩ}$	IRFB4229PBF $R_{DS(on)}=46.0\text{ mΩ}$	IRFP4229PBF $R_{DS(on)}=46.0\text{ mΩ}$		BSZ16DN25NS3 G $R_{DS(on)}=165.0\text{ mΩ}$	IRFH5025 $R_{DS(on)}=100.0\text{ mΩ}$	
				IPP600N25N3 G $R_{DS(on)}=60.0\text{ mΩ}$		IPC045N25N3 $R_{DS(on)}=146.0\text{ mΩ}$	BSZ42DN25NS3 G $R_{DS(on)}=425.0\text{ mΩ}$	BSC16DN25NS3 G $R_{DS(on)}=165.0\text{ mΩ}$	

OptiMOS™ and StrongIRFET™ 300 V normal level



$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-263 (D ² PAK)	TO-220	TO-247	SuperSO8
0-25			IRF300P226 $R_{DS(on)}=19.0\text{ mΩ}$	
>25	IPB407N30N $R_{DS(on)}=40.7\text{ mΩ}$	IPP410N30N $R_{DS(on)}=41.0\text{ mΩ}$	IRFP4868PBF $R_{DS(on)}=32.0\text{ mΩ}$	
			IRF300P227 $R_{DS(on)}=40.0\text{ mΩ}$	
		IRFB4137PBF $R_{DS(on)}=69.0\text{ mΩ}$	IRFP4137PBF $R_{DS(on)}=69.0\text{ mΩ}$	BSC13DN30NSFD $R_{DS(on)}=130.0\text{ mΩ}$

Small signal P-channel



Voltage [V]		SOT-223	TSOP-6	SOT-89	SC59	SOT-23	SOT-323	SOT-363
P-channel MOSFETs	-250	BSP317P 4 Ω, -0.43 A, LL		BSS192P 12 Ω, -0.19 A, LL	BSR92P 11 Ω, -0.14 A, LL			
		BSP92P 12 Ω, -0.26 A, LL						
	-100	BSP321P 900 mΩ, -0.98 A, NL						
		BSP322P 800 mΩ, -1.0 A, LL						
		BSP316P 1.8 Ω, -0.68 A, LL			BSR316P 1.8 Ω, -0.36 A, LL			
	-60	BSP612P 120 mΩ, 3 A, LL				ISS17EP06LM 1.7Ω, -0.3 A, LL		
		BSP613P 130 mΩ, 2.9 A, NL				BSS83P 2 Ω, -0.33 A, LL	BSS84PW 8 Ω, -0.15 A, LL	
		BSP170P 300 mΩ, -1.9 A, NL				ISS55EP06LM 5.5 Ω, -0.18 A, NL		
		BSP171P 300 mΩ, -1.9 A, LL				BSS84P 8 Ω, -0.17 A, LL		
		BSP315P 800 mΩ, -1.17 A, LL						
		ISP650P06NM 65 mΩ, -3.7 A, NL			BSR315P 800 mΩ, -0.62 A, LL			
		ISP12DP06NM 125 mΩ, -2.8, NL						
		ISP25DP06LM 250 mΩ, -1.9 A, LL						
		ISP25DP06NM 250 mΩ, -1.9 A, NL						
		ISP75DP06LM 750 mΩ, -1.1 A, LL						
	-30		BSL303SPE 33 mΩ, -6.3 A, LL			BSS308PE 80 mΩ, -2.1 A, LL, ESD		BSD314SPE 140 mΩ, -1.5 A, LL, ESD
			IRFTS9342TRPBF* 40 mΩ, -5.8 A, LL			BSS314PE 140 mΩ, -1.5 A, LL, ESD		
			BSL307SP 43 mΩ, -5.5 A, LL			BSS315P 150 mΩ, -1.5 A, LL		
			BSL305SPE 45 mΩ, -5.5 A, LL					
			BSL308PE 80 mΩ, -2.1 A, LL, dual, ESD					
			BSL314PE 140 mΩ, -1.5 A, LL, ESD, dual					
	-20		BSL207SP 41 mΩ, -6 A, SLL			IRLML2244* ¹⁾ 54 mΩ, 4.3 A, LL		
			BSL211SP 67 mΩ, -4.7 A, SLL			IRLML2246* ¹⁾ 135 mΩ, 2.6 A, LL	BSS209PW 550 mΩ, -0.58 A, SLL	BSV236SP 175 mΩ, -1.5 A, SLL
						BSS215P 150 mΩ, -1.5 A, SLL	BSS223PW 1.2 Ω, -0.39 A, SLL	BSD223P 1.2 Ω, -0.39 A, SLL, dual

Small signal complementary



Voltage [V]		SOT-223	TSOP-6	SOT-89	SC59	SOT-23	SOT-323	SOT-363
Complementary	-20/20		BSL215C N: 140 mΩ, 1.5 A, SLL P: 150 mΩ, 1.5 A, SLL					BSD235C N: 350 mΩ, 0.95 A, SLL P: 1.2 Ω, 0.53 A, SLL
	-30/30		BSL308C N: 57 mΩ, 2.3 A, LL P: 80 mΩ, -2.0 A, LL					
			BSL316C N: 160 mΩ, 1.4 A, LL P: 150 mΩ, -1.5 A, LL					

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All products are qualified to Automotive AEC Q101 (except the parts marked with *)

1) R_{DS(on)} 4.5 V rated



Small signal N-channel

Voltage [V]		SOT-223	TSOP-6	SOT-89	SC59	SOT-23	SOT-323	SOT-363
N-channel	20		BSL802SN 22 mΩ, 7.5 A, ULL		BSR802N 23 mΩ, 3.7 A, ULL	IRLML6244* ¹⁾ 21 mΩ, 6.3 A, LL		
			BSL202SN 22 mΩ, 7.5 A, SLL		BSR202N 21 mΩ, 3.8 A, SLL	IRLML6246* ¹⁾ 46 mΩ, 4.1 A, LL		
			BSL205N 50 mΩ, 2.5 A, SLL, dual			BSS205N 50 mΩ, 2.5 A, SLL		BSD214SN 140 mΩ, 1.5 A, SLL
						BSS806NE 57 mΩ, 2.3 A, ULL, ESD		BSD816SN 160 mΩ, 1.4 A, ULL
			BSL207N 70 mΩ, 2.1 A, SLL, dual			BSS806N 57 mΩ, 2.3 A, ULL	BSS214NW 140 mΩ, 1.5 A, SLL	BSD235N 350 mΩ, 0.95 A, SLL, dual
			BSL214N 140 mΩ, 1.5 A, SLL, dual			BSS214N 140 mΩ, 1.5 A, SLL	BSS816NW 160 mΩ, 1.4 A, ULL	BSD840N 400 mΩ, 0.88 A, ULL, dual
	25					IRFML8244* 24 mΩ, 5.8 A, NL		
	30		IRLTS6342* ¹⁾ 17.5 mΩ, 8.3 A, LL		BSR302N 23 mΩ, 3.7 A, LL	IRLML0030* 27 mΩ, 5.3 A, LL		BSD316SN 160 mΩ, 1.4 A, LL
			IRFTS8342* 19 mΩ, 8.2 A, NL			IRLML6344* ¹⁾ 29 mΩ, 5.0 A, LL		
			BSL302SN 25 mΩ, 7.1 A, LL			BSS306N 57 mΩ, 2.3 A, LL		
			BSL306N 57 mΩ, 2.3 A, LL, dual			IRLML6346* ¹⁾ 63 mΩ, 3.4 A, LL		
						IRLML2030* 100 mΩ, 1.4 A, LL		
						BSS316N 160 mΩ, 1.4 A, LL		
	55					BSS670S2L 650 mΩ, 0.54 A, LL	BSS340NW 400 mΩ, 0.88 A, LL	
	60	BSP318S 90 mΩ, 2.6 A, LL	BSL606SN 60 mΩ, 4.5 A, LL	BSS606N 60 mΩ, 3.2 A, LL	BSR606N 60 mΩ, 2.3 A, LL	IRLML0060* 92 mΩ, 2.7 A, LL	BSS138W 3.5 Ω, 0.28 A, LL	2N7002DW 3 Ω, 0.3 A, LL, dual
		BSP320S 120 mΩ, 2.9 A, NL				IRLML2060* 480 mΩ, 1.2 A, LL	SN7002W 5 Ω, 0.23 A, LL	
		BSP295 300 mΩ, 1.8 A, LL				BSS138N 3.5 Ω, 0.23 A, LL		
						BSS7728N 5 Ω, 0.2 A, LL		
						SN7002N 5 Ω, 0.2 A, LL		
						2N7002 3 Ω, 0.3 A, LL		
	75	BSP716N 160 mΩ, 2.3 A, LL	BSL716SN 150 mΩ, 2.5 A, LL			BSS159N 8 Ω, 0.13 A, depl.		
	80							
	100	BSP372N 230 mΩ, 1.8 A, LL	BSL372SN 220 mΩ, 2.0 A, LL			IRLML0100* 220 mΩ, 1.6 A, LL		
		BSP373N 240 mΩ, 1.8 A, NL	BSL373SN 230 mΩ, 2.0 A, NL			BSS119N 6 Ω, 0.19 A, LL V _{GS(th)} 1.8 V to 2.3 V		
		BSP296N 600 mΩ, 1.2 A, LL	BSL296SN 460 mΩ, 1.4 A, LL			BSS123N 6 Ω, 0.19 A, LL V _{GS(th)} 0.8 V to 1.8 V		
						BSS169 12 Ω, 0.09 A, depl.		
	200	BSP297 1.8 Ω, 0.66 A, LL						
		BSP149 3.5 Ω, 0.14 A, depl.						
	240	BSP88 6 Ω, 0.35 A, 2.8 V rated		BSS87 6 Ω, 0.26 A, LL		BSS131 14 Ω, 0.1 A, LL		
		BSP89 6 Ω, 0.35 A, LL						
		BSP129 6 Ω, 0.05 A, depl.						
	250					BSS139 30 Ω, 0.03 A, depl.		
	400	BSP298 3 Ω, 0.5 A, NL						
		BSP179 24 Ω, 0.04 A, depl.						
		BSP324 25 Ω, 0.17 A, LL						
	500	BSP299 4 Ω, 0.4 A, NL						
	600	BSP125 45 Ω, 0.12 A, LL		BSS225 45 Ω, 0.09 A, LL		BSS127 500 Ω, 0.023 A, LL		
		BSP135 60 Ω, 0.02 A, depl.				BSS126 700 Ω, 0.007 A, depl.		
	800	BSP300 20 Ω, 0.19 A, NL						

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All products are qualified to Automotive AEC Q101 (except 2N7002) (except the parts marked with *)

1) R_{DS(on)} specified at 4.5 V

Power P-channel MOSFETs



Voltage [V]	TO-252 (DPAK)	DirectFET™	SOT-23	PQFN 3.3 x 3.3	SuperSO8	SO-8	PQFN 2 x 2	TSOP-6
-20						BSO201SP H $R_{DS(on)} = 7.0 \text{ m}\Omega$		
						BSO203SP H $R_{DS(on)} = 21.0 \text{ m}\Omega$		
						BSO203P H $R_{DS(on)} = 21.0 \text{ m}\Omega$		
							IRLHS2242TRPBF** $R_{DS(on)} = 31.0 \text{ m}\Omega$	IRLTS2242 $R_{DS(on)} = 39 \text{ m}\Omega$
			IRLML2244 ²⁾ *** $R_{DS(on)} = 54 \text{ m}\Omega$			BSO207P H $R_{DS(on)} = 45.0 \text{ m}\Omega$		
			IRLML2246 ²⁾ *** $R_{DS(on)} = 135 \text{ m}\Omega$			BSO211P H $R_{DS(on)} = 67.0 \text{ m}\Omega$		
					BSC030P03NS3 G $R_{DS(on)} = 3.0 \text{ m}\Omega$	IRF9310 $R_{DS(on)} = 4.6 \text{ m}\Omega$		
					BSC060P03NS3E G $R_{DS(on)} = 6.0 \text{ m}\Omega$; ESD	IRF9317 $R_{DS(on)} = 6.6 \text{ m}\Omega$		
				BSZ086P03NS3 G $R_{DS(on)} = 8.6 \text{ m}\Omega$		IRF9321 $R_{DS(on)} = 7.2 \text{ m}\Omega$		
	IPD042P03L3 G $R_{DS(on)} = 4.2 \text{ m}\Omega$			BSZ086P03NS3E G $R_{DS(on)} = 8.6 \text{ m}\Omega$		BSO080P03NS 3 G $R_{DS(on)} = 8.0 \text{ m}\Omega$		
	SPD50P03L G ¹⁾ * $R_{DS(on)} = 7.0 \text{ m}\Omega$	IRF9395M $R_{DS(on)} = 7.0 \text{ m}\Omega$; dual			BSC084P03NS3 G $R_{DS(on)} = 8.4 \text{ m}\Omega$	BSO080P03NS3E G $R_{DS(on)} = 8.0 \text{ m}\Omega$; ESD		
					BSC084P03NS3E G $R_{DS(on)} = 8.4 \text{ m}\Omega$; ESD	BSO080P03S H $R_{DS(on)} = 8.0 \text{ m}\Omega$		
				BSZ120P03NS3 G $R_{DS(on)} = 12.0 \text{ m}\Omega$		BSO301SP H $R_{DS(on)} = 8.0 \text{ m}\Omega$		
				BSZ120P03NS3E G $R_{DS(on)} = 12.0 \text{ m}\Omega$; ESD		IRF9328 $R_{DS(on)} = 11.9 \text{ m}\Omega$		
-30						IRF9388TRPBF $R_{DS(on)} = 11.9 \text{ m}\Omega$		
						BSO130P03S H $R_{DS(on)} = 13.0 \text{ m}\Omega$		
						IRF9358 $R_{DS(on)} = 16 \text{ m}\Omega$; dual		
				IRFHM9331 ²⁾ $R_{DS(on)} = 15 \text{ m}\Omega$		IRF9332 $R_{DS(on)} = 17.5 \text{ m}\Omega$		
						IRF9392TRPBF $R_{DS(on)} = 17.5 \text{ m}\Omega$		
				BSZ180P03NS3 G $R_{DS(on)} = 18.0 \text{ m}\Omega$		IRF9333 $R_{DS(on)} = 19.4 \text{ m}\Omega$		
				BSZ180P03NS3E G $R_{DS(on)} = 18.0 \text{ m}\Omega$; ESD		BSO200P03S H $R_{DS(on)} = 20.0 \text{ m}\Omega$		
						BSO303SP H $R_{DS(on)} = 21.0 \text{ m}\Omega$	IRFH9301TRPBF $R_{DS(on)} = 37.0 \text{ m}\Omega$	
			IRLML9301TRPBF $R_{DS(on)} = 64 \text{ m}\Omega$			BSO303P H $R_{DS(on)} = 21.0 \text{ m}\Omega$; dual		
			IRLML9303TRPBF $R_{DS(on)} = 165 \text{ m}\Omega$			IRF9362 $R_{DS(on)} = 21 \text{ m}\Omega$; dual	IRFHS9351TRPBF $R_{DS(on)} = 170.0 \text{ m}\Omega$; dual	IRFHS9342*** $R_{DS(on)} = 32 \text{ m}\Omega$
						IRF9335 $R_{DS(on)} = 59 \text{ m}\Omega$		



Power P-channel MOSFETs



Voltage [V]			TO-252 (DPAK)	TO-263 (D ² PAK)	TO-220	PQFN 3.3 x 3.3	SuperSO8	SO-8
P-channel MOSFETs	-60	IPD380P06NM $R_{DS(on)} = 38 \text{ m}\Omega$	IPB110P06LM $R_{DS(on)} = 11 \text{ m}\Omega$	SPP80P06P H* $R_{DS(on)} = 23.0 \text{ m}\Omega$				
		IPD650P06NM $R_{DS(on)} = 65 \text{ m}\Omega$	SPB80P06P G* $R_{DS(on)} = 23.0 \text{ m}\Omega$					
		SPD30P06P G* $R_{DS(on)} = 75.0 \text{ m}\Omega$						
		IPD900P06NM $R_{DS(on)} = 90 \text{ m}\Omega$						
		SPD18P06P G* $R_{DS(on)} = 130.0 \text{ m}\Omega$	SPB18P06P G* $R_{DS(on)} = 130.0 \text{ m}\Omega$	SPP18P06P H* $R_{DS(on)} = 130.0 \text{ m}\Omega$				BSO613SPV G* $R_{DS(on)} = 130.0 \text{ m}\Omega$
		SPD09P06PL G* $R_{DS(on)} = 250.0 \text{ m}\Omega$						
		IPD25DP06LM $R_{DS(on)} = 250 \text{ m}\Omega$						
		IPD25DP06NM $R_{DS(on)} = 250 \text{ m}\Omega$						
		SPD08P06P G* $R_{DS(on)} = 300.0 \text{ m}\Omega$	SPB08P06P G* $R_{DS(on)} = 300.0 \text{ m}\Omega$	SPP08P06P H* $R_{DS(on)} = 300.0 \text{ m}\Omega$				
		IPD40DP06NM $R_{DS(on)} = 400 \text{ m}\Omega$						
	-100	SPD15P10PL G* $R_{DS(on)} = 200.0 \text{ m}\Omega$		SPP15P10PL H* $R_{DS(on)} = 200.0 \text{ m}\Omega$				
		SPD15P10P G* $R_{DS(on)} = 240.0 \text{ m}\Omega$		SPP15P10P H* $R_{DS(on)} = 240.0 \text{ m}\Omega$				
		SPD04P10PL G* $R_{DS(on)} = 850.0 \text{ m}\Omega$						
		SPD04P10P G* $R_{DS(on)} = 1000.0 \text{ m}\Omega$						

Power MOSFETs complementary



Voltage [V]			TO-252 (DPAK)	TO-263 (D ² PAK)	TO-220	PQFN 3.3 x 3.3	SuperSO8	SO-8
Complementary	-20/20	>50 mΩ				BSZ15DC02KD H** N: 55 mΩ, 5.1 A P: 150 mΩ, -3.2 A		
						BSZ215C H** N: 55 mΩ, 5.1 A P: 150 mΩ, -3.2 A		
	-60/60	11-30 Ω						BSO612CV G* N: 0.12 Ω, 3.0 A P: 0.30 Ω, -2.0 A
								BSO615C G* N: 0.11 Ω, 3.1 A P: 0.30 Ω, -2.0 A

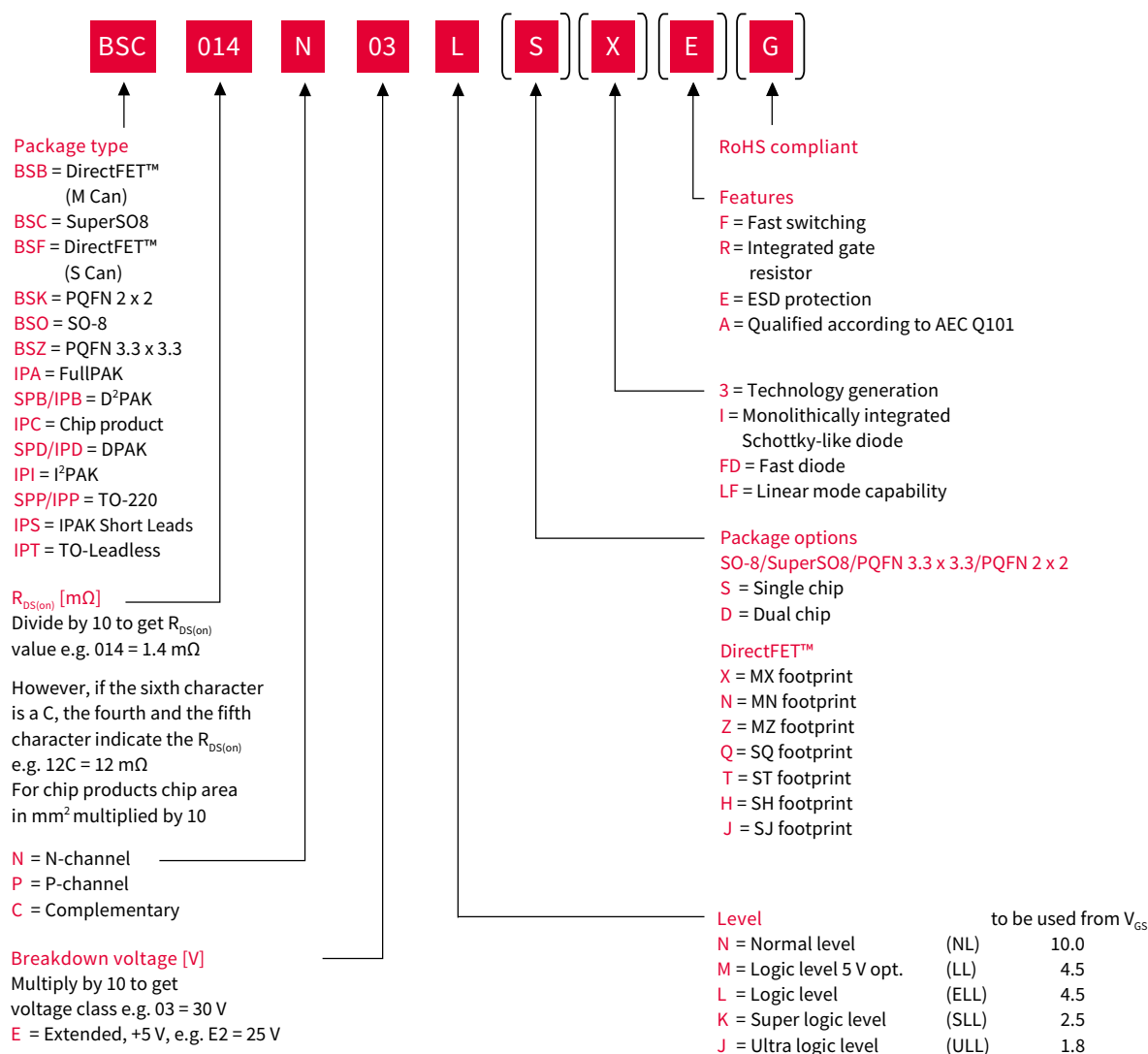
www.infineon.com/complementary

*Products are qualified to Automotive AEC Q101

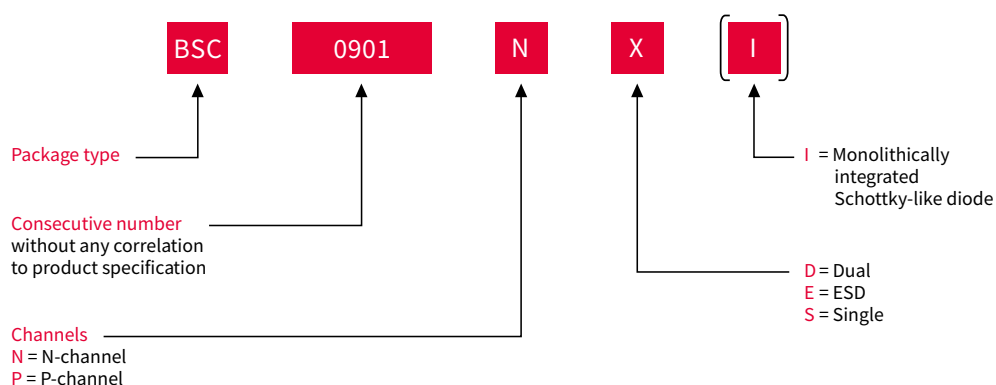
** $R_{DS(on)}$ specified at 4.5 V

Nomenclature

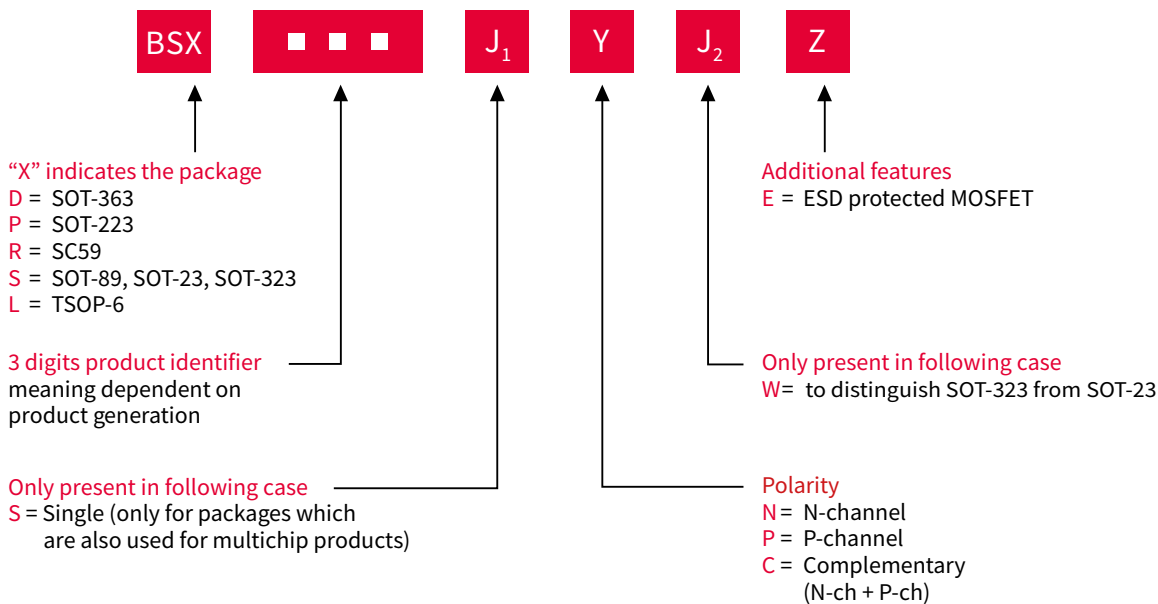
OptiMOS™



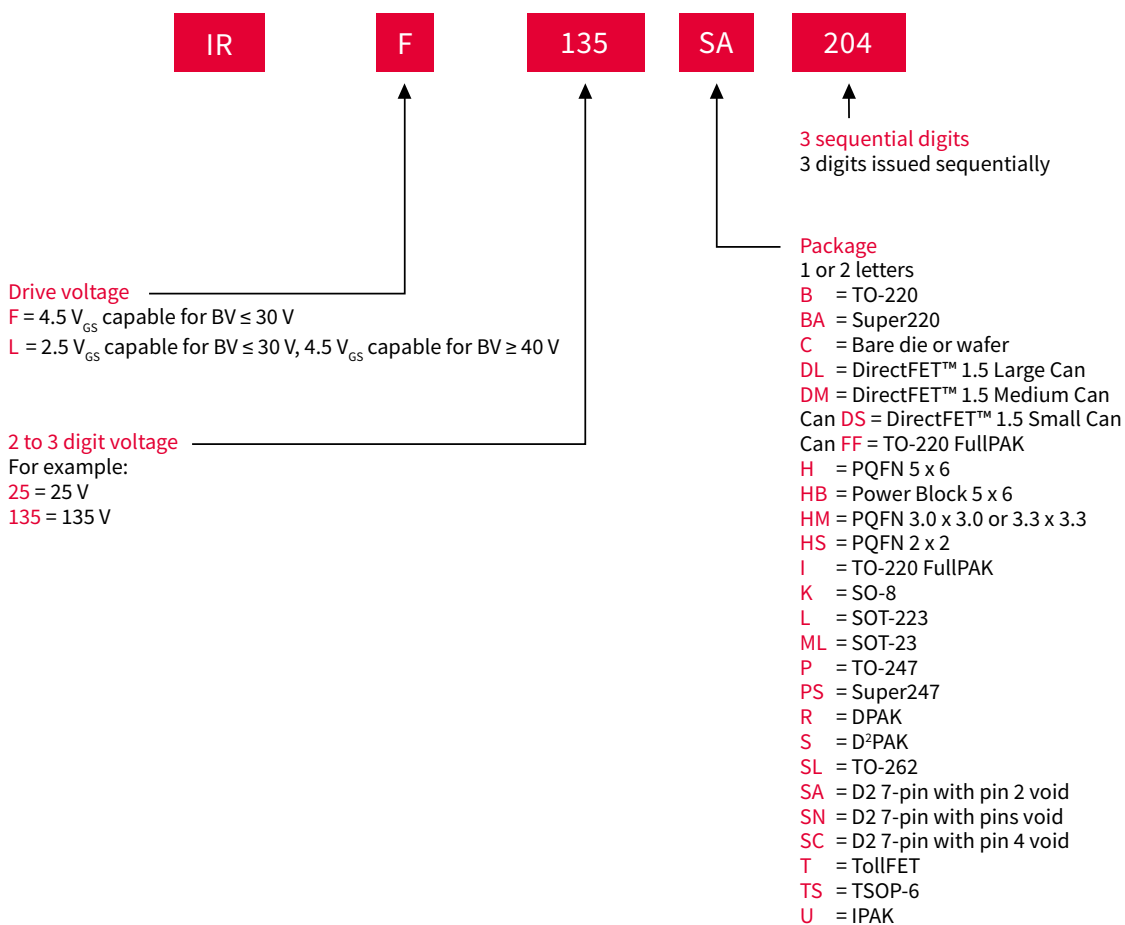
OptiMOS™ 30 V



Small signal



StrongIRFET™ (from May 2015 onwards)





Infineon support for low voltage MOSFETs

Useful links and helpful information

Further information, data sheets and documents

www.infineon.com/powermosfet-12V-300V

www.infineon.com/smallsignal

www.infineon.com/pchannel

www.infineon.com/depletion

www.infineon.com/complementary

www.infineon.com/baredie

Evaluation boards and simulation models

www.infineon.com/to-leadless-evaluationboard

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